

Centre for Computational Structural and Materials Mechanics

Overall mechanical properties of polysilicon films: homogenization vs Monte Carlo simulations



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Workshop

Impact of mechanical and
thermal loads on the long
term stability of PV modules

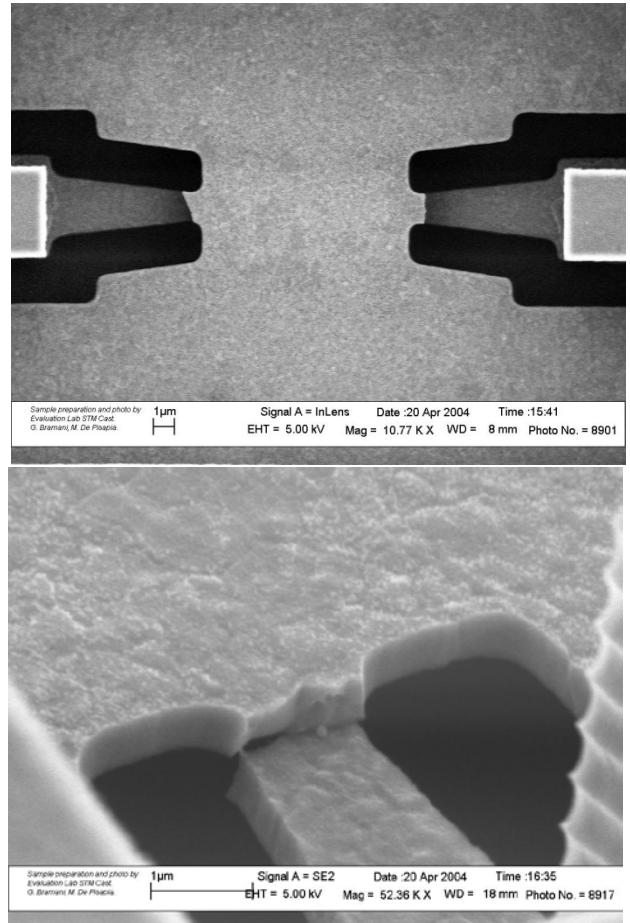
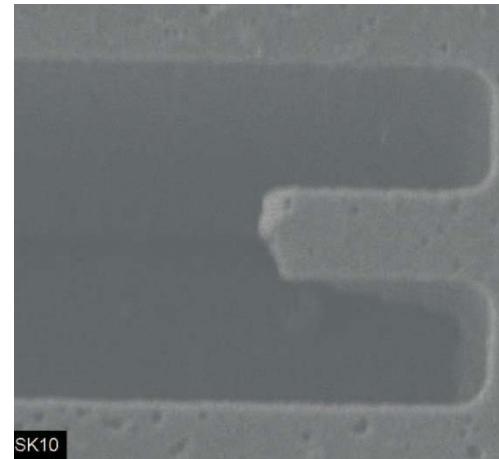
Politecnico di Milano

Dipartimento di Ingegneria Civile e Ambientale

ENGINEERING MOTIVATION:

failure of **POLYSILICON** inertial MEMS sensors exposed to accidental drops or shocks

Due to accidental drops/shocks,
the most stressed details of inertial MEMS sensors
(suspension springs) can break because of
the propagation of inter- and/or trans-granular cracks



Sacrificial layer

Substrate

Mechanical layer

Sacrificial layer

Substrate

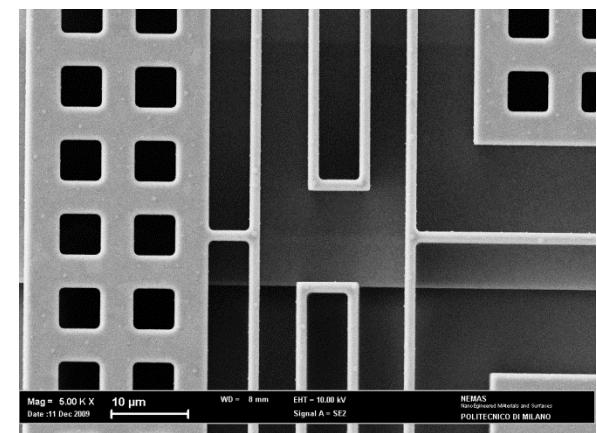
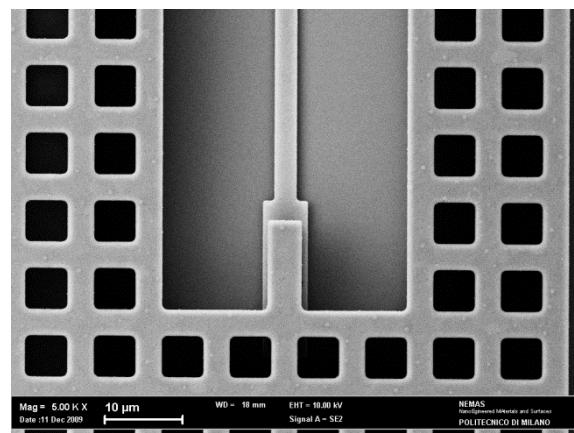
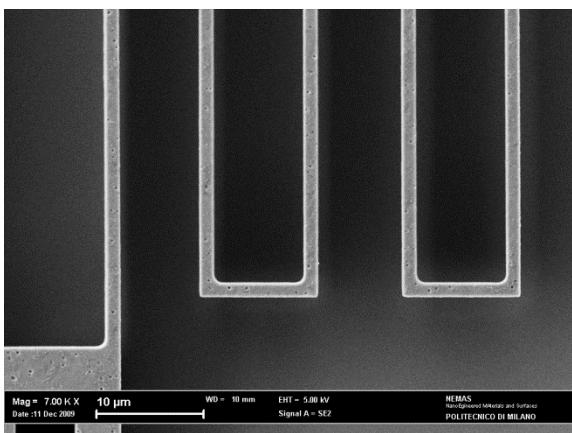
Mechanical layer

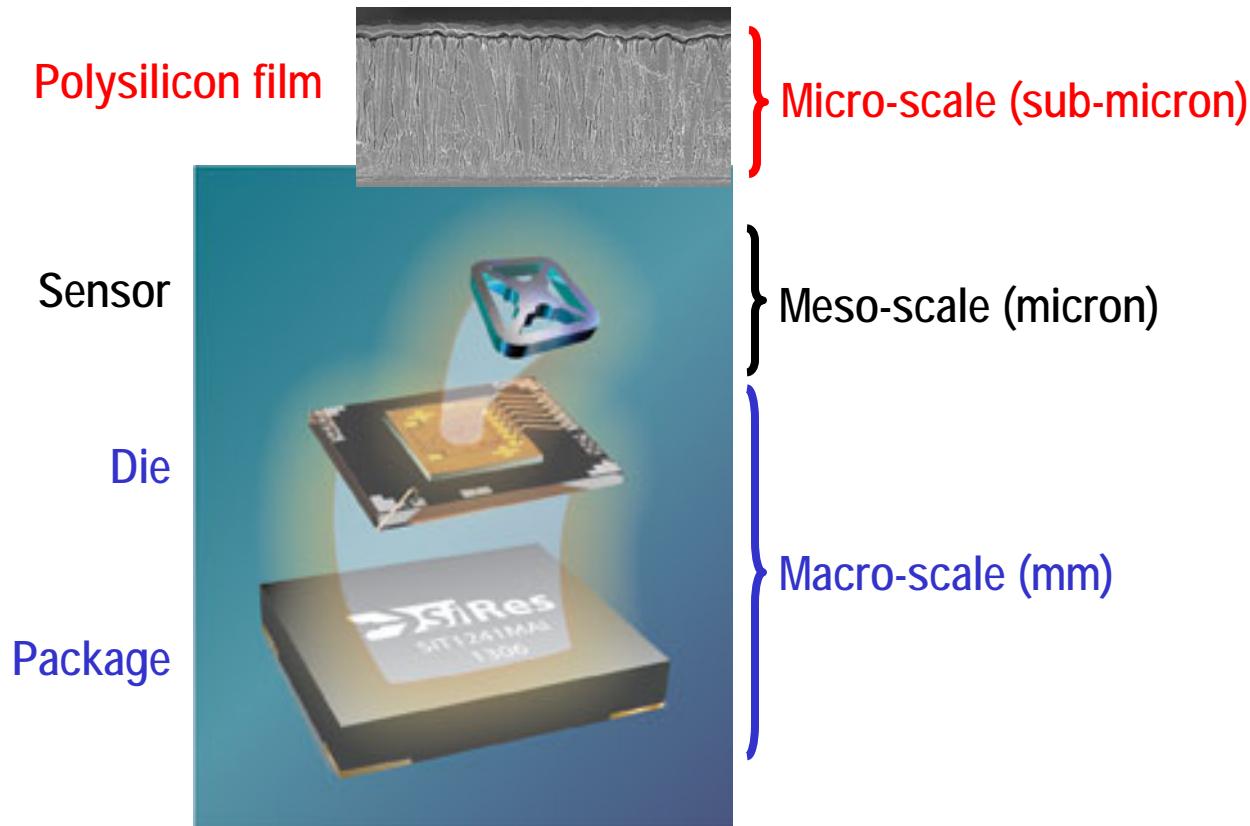
Substrate

deposition of the oxide sacrificial layer

deposition of the silicon structural layer

oxide Removal



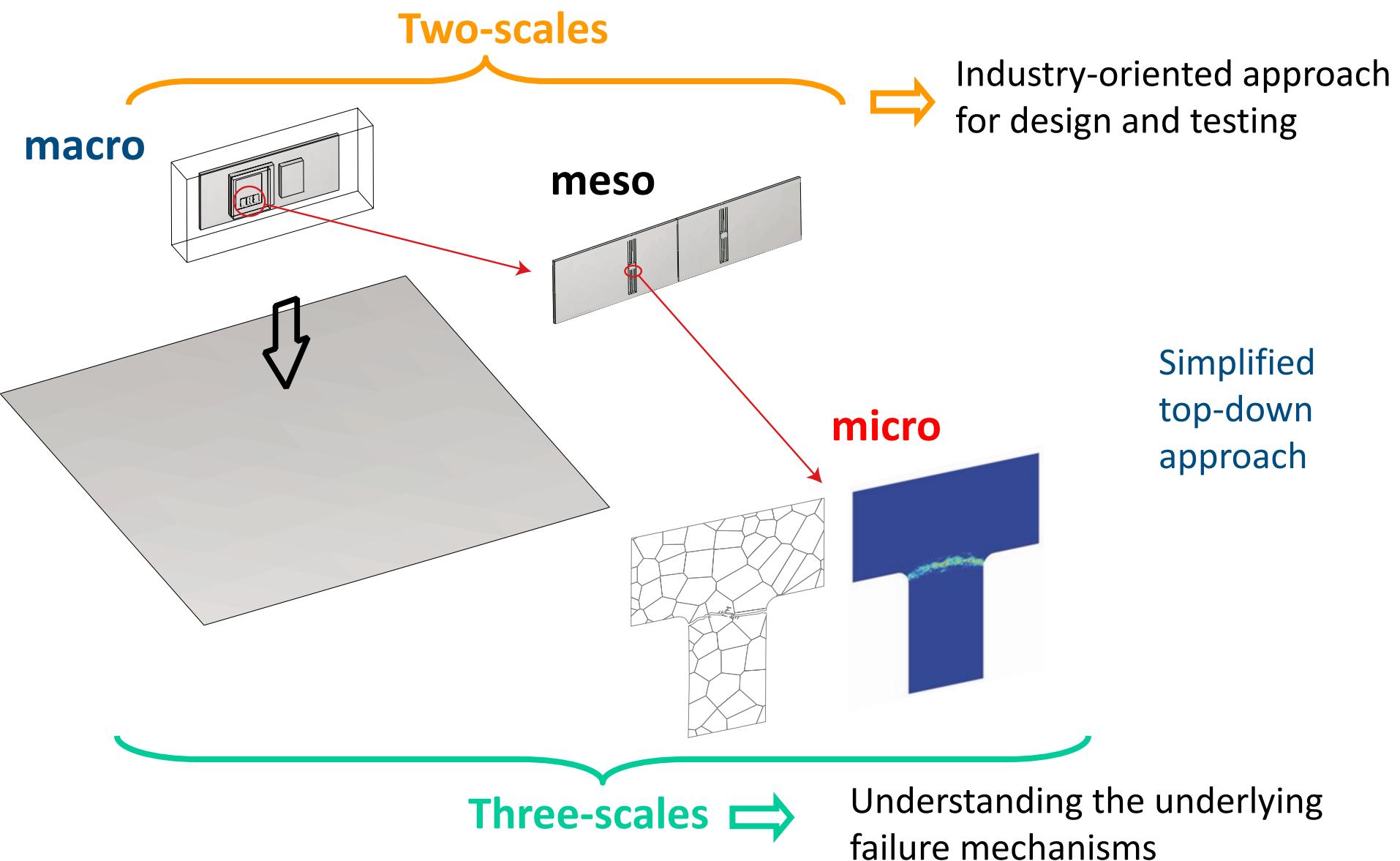


Multi-scale analysis of MEMS subject to impacts:

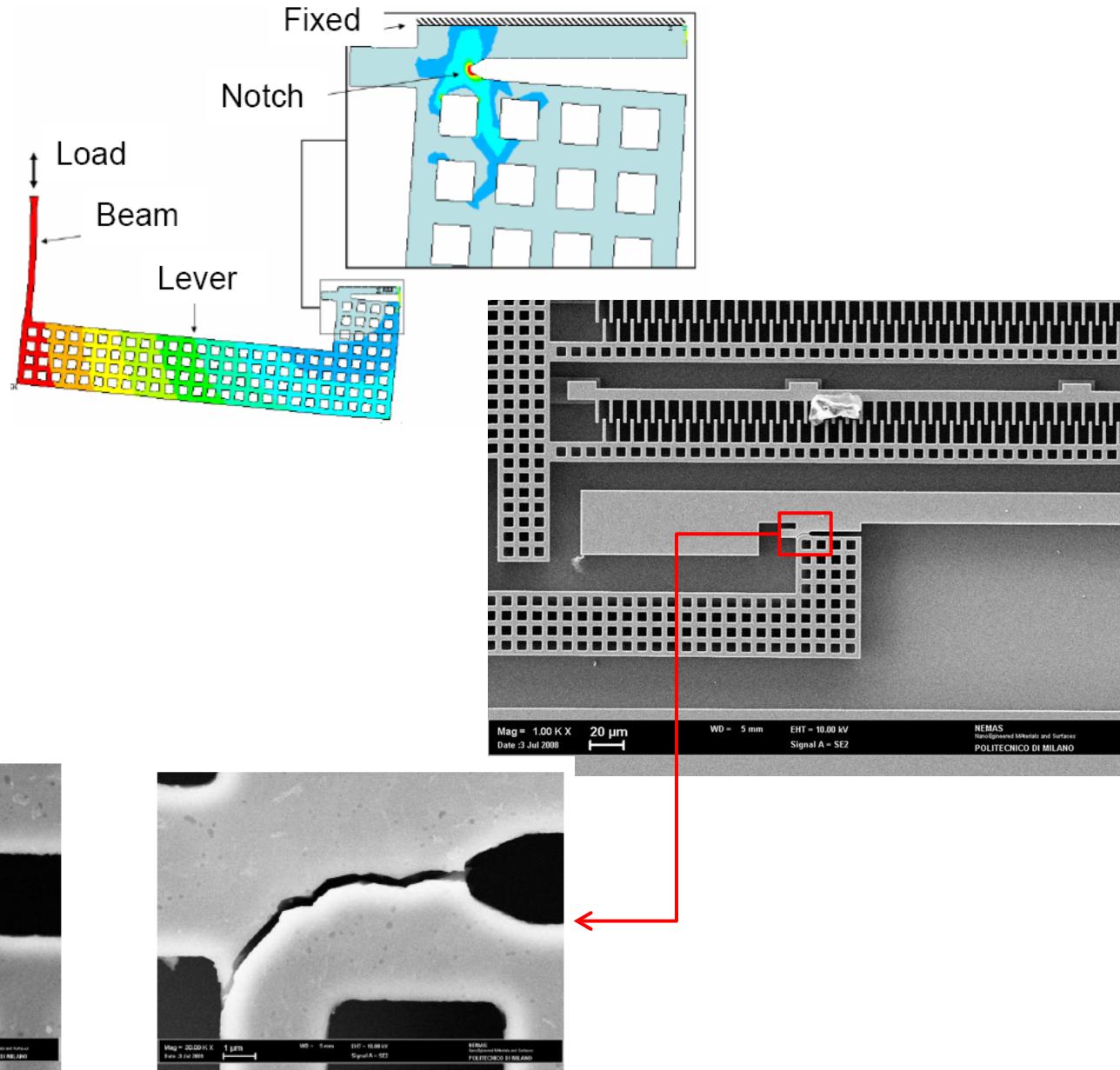
- decoupling between macro-scale and meso-scale allowed by small inertia of the sensor
- decoupling between meso-scale and micro-scale?
(not allowed if nonlinear effects to be simulated)

	mass (Kg)
Package	$5 \cdot 10^{-4}$
Die	$2.3 \cdot 10^{-6}$
Sensor	$3 \cdot 10^{-9}$

Multi-scale analysis of shock-induced failure of polysilicon MEMS accelerometers



On-chip testing (crack and fatigue)



MACRO-SCALE simulations:

effect of drop features (drop height, falling orientation) on acceleration/displacement histories at anchors.

Tool: commercial FE code, 3D models

MESO-SCALE simulations:

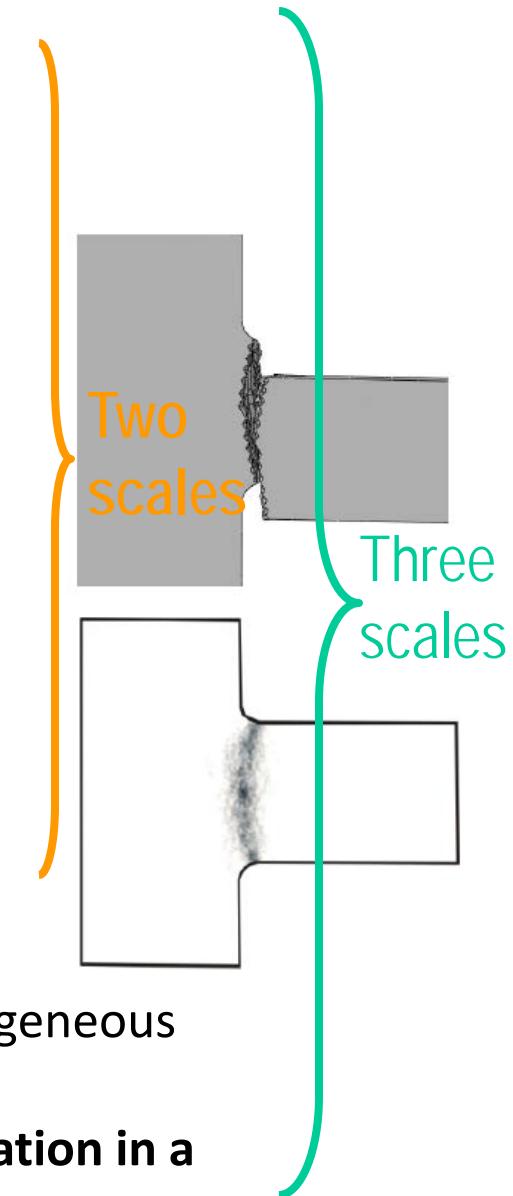
link between drop features (drop height, falling orientation) and sensor failure probability. In 3S analyses, localization of most stressed sensor regions and input definition for micro-scale analysis.

Tool: commercial FE code, 3D models + material **failure criterion**

MICRO-SCALE simulations:

influence of the microstructure on failure mechanisms, heterogeneous (polycrystalline) material.

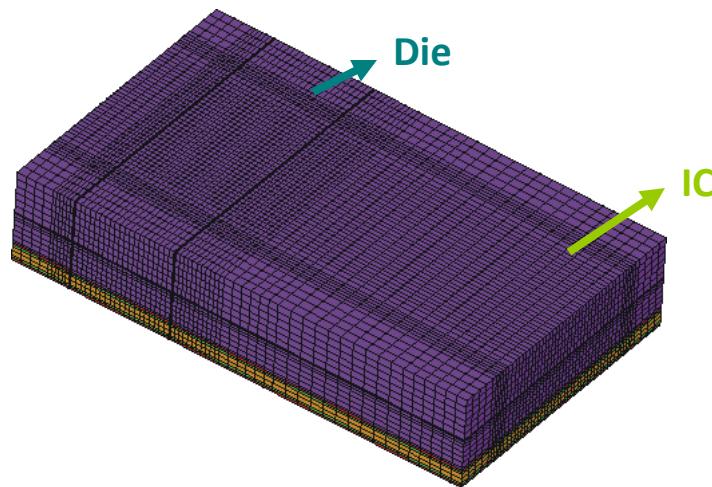
Tool: research code to **simulate fracture initiation and propagation in a polycrystal**, Monte Carlo simulations



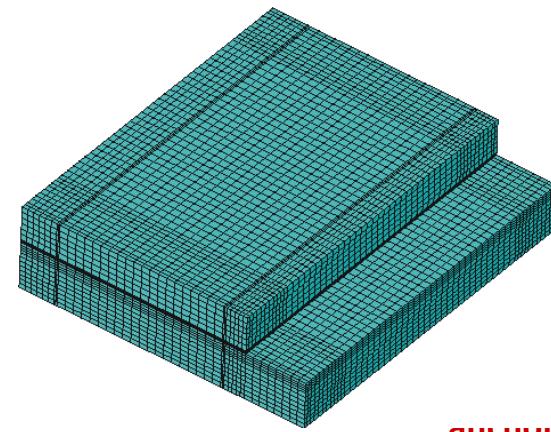
1. S. Mariani, A. Ghisi, A. Corigliano, S. Zerbini. Multi-scale analysis of MEMS sensors subject to drop impacts. *Sensors*, **7**, pp. 1817-1833, 2007.
2. S. Mariani, A. Ghisi, F. Fachin, F. Cacchione, A. Corigliano, S. Zerbini. A three-scale FE approach to reliability analysis of MEMS sensors subject to impacts. *Meccanica*, **43**, pp. 469-483, 2008.
3. A. Ghisi, F. Fachin, S. Mariani, S. Zerbini. Multi-scale analysis of polysilicon MEMS sensors subject to accidental drops: Effect of packaging. *Microelectronics Reliability*, **49**, pp. 340-349, 2009.
4. S. Mariani, A. Ghisi, A. Corigliano, S. Zerbini. Modeling impact-induced failure of polysilicon MEMS: a multi-scale approach. *Sensors*, **9**, pp. 556-567, 2009.
5. S. Mariani, R. Martini, A. Ghisi, A. Corigliano, B. Simoni. Monte Carlo simulation of micro-cracking in polysilicon MEMS exposed to shocks. *International Journal of Fracture*, **167**, pp. 83-101, 2011.
6. A. Ghisi, S. Kalicinski, S. Mariani, I. De Wolf, A. Corigliano. Polysilicon MEMS accelerometers exposed to shocks: numerical-experimental investigation. *Journal of Micromechanics and Microengineering*, **19**, 035023, 2009.
7. S. Mariani, A. Ghisi, A. Corigliano, R. Martini, B. Simoni. Two-scale simulation of drop-induced failure of polysilicon MEMS sensors. *Sensors*, **11**, pp. 4972-4989, 2011.
8. A. Ghisi, S. Mariani, A. Corigliano, S. Zerbini. Physically-based reduced order modelling of a uni-axial polysilicon MEMS accelerometer. *Sensors*, **12**, pp. 13985-14003, 2012.
9. S. Mariani, R. Martini, A. Ghisi, A. Corigliano, M. Beghi. Overall elastic properties of polysilicon films: a statistical investigation of the effects of polycrystal morphology. *International Journal for Multiscale Computational Engineering*, **9**, pp. 327-346, 2011.
10. S. Mariani, R. Martini, A. Corigliano, M. Beghi. Overall elastic domain of thin polysilicon films. *Computational Materials Science*, **50**, pp. 2993-3004, 2011.
11. F. Confalonieri. A domain decomposition approach for the simulation of fracture phenomena in polycrystalline microsystems. *PhD Thesis*, 2013.
12. F. Confalonieri, G. Cocchetti, A. Ghisi, A. Corigliano. A domain decomposition method for the simulation of fracture in polysilicon MEMS. *Microelectronics Reliability*, in press.
13. A. Corigliano, M. Dossi, S. Mariani. Domain decomposition and model order reduction methods applied to the simulation of multiphysics problems in MEMS. *Computers and Structures*, **122**, pp. 113–127, 2013.

Overview of a studied device (uni-axial MEMS accelerometer)

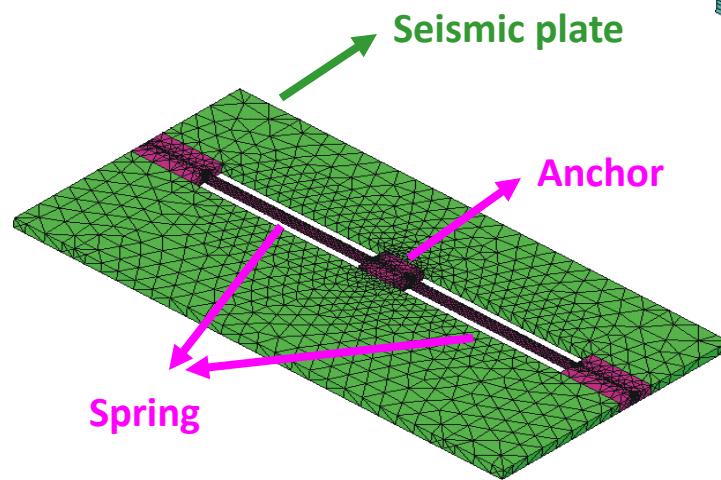
► Package
(macro-scale)

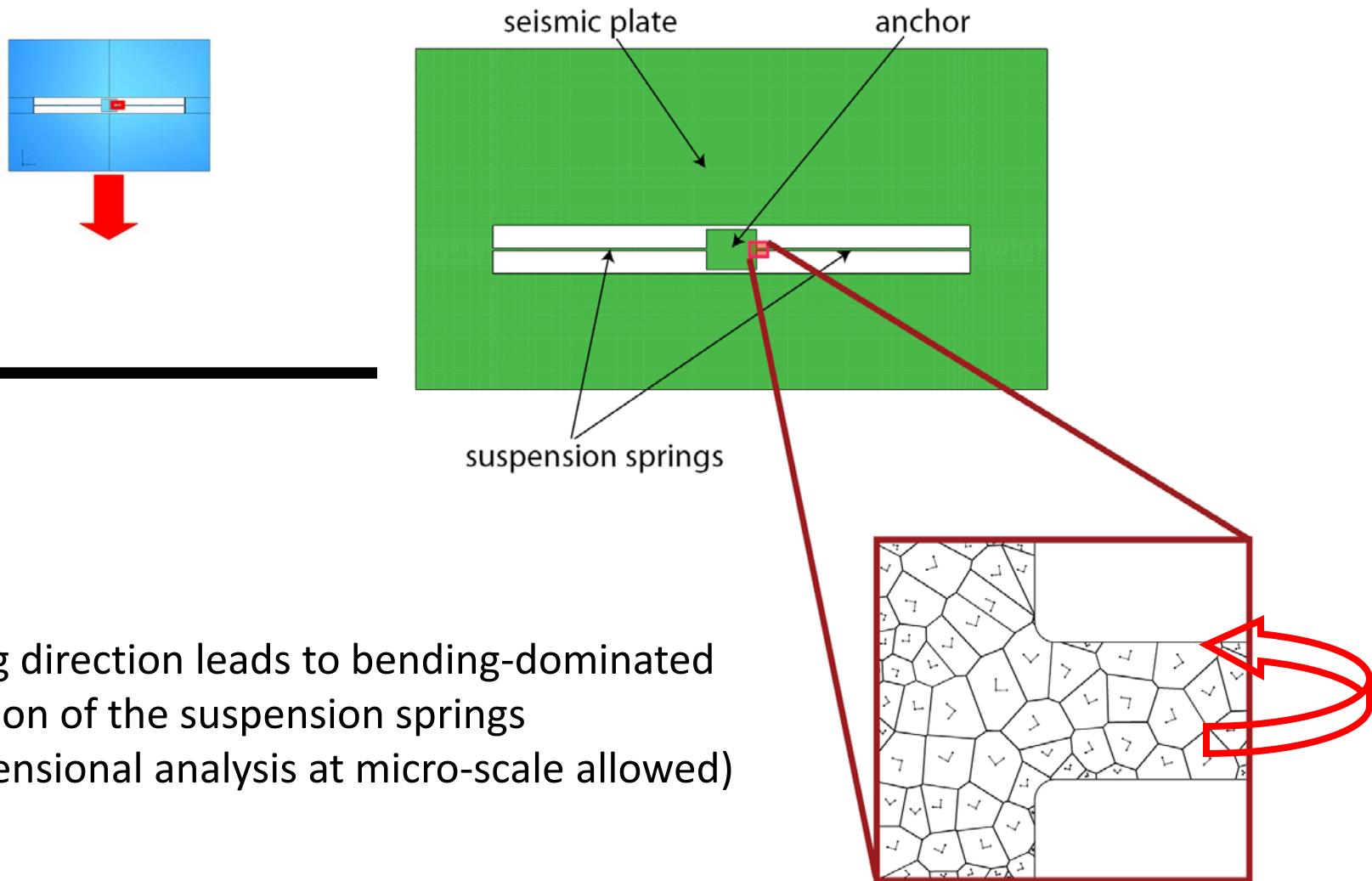


► Die (macro-scale)



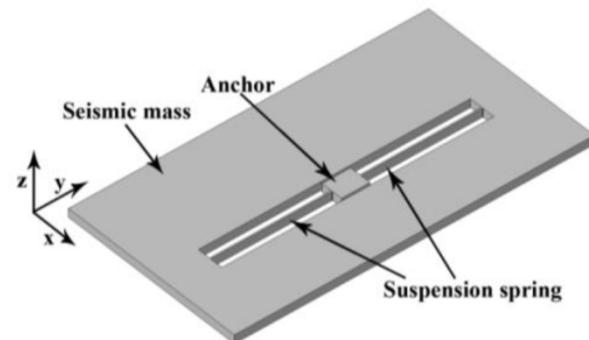
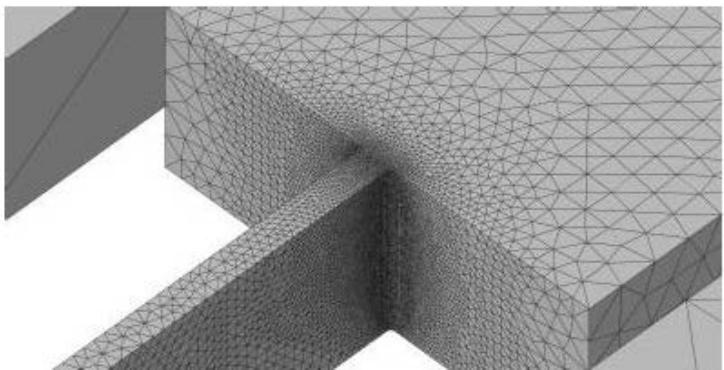
► Sensor
(meso-scale)



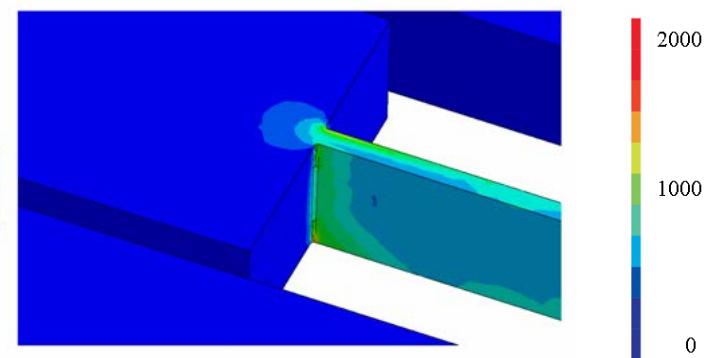
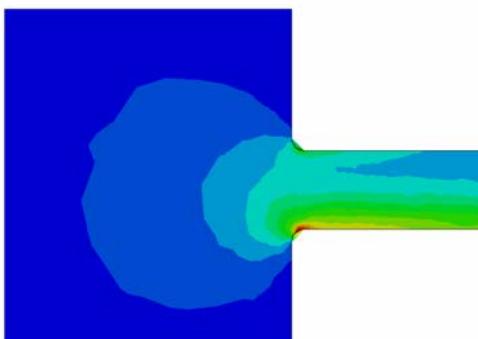


The falling direction leads to bending-dominated deformation of the suspension springs
(two-dimensional analysis at micro-scale allowed)

Adopted space discretization ($d_e = 100 \text{ nm}$)

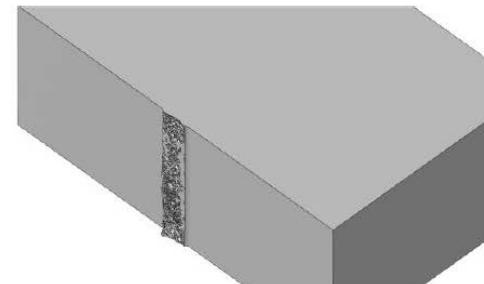
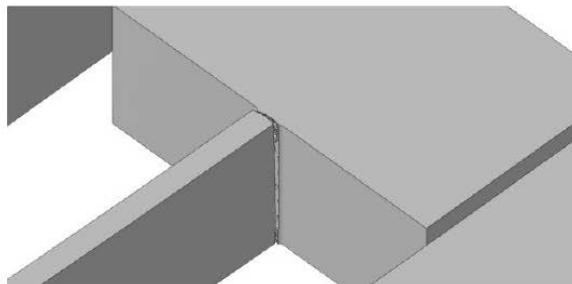


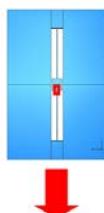
(MPa)



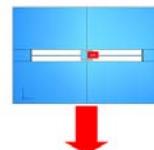
Local stress intensification
close to the anchor point

Forecasted failure mode
(smeared-crack approach
using Abaqus)

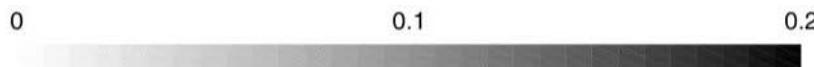




tension-dominated
loading

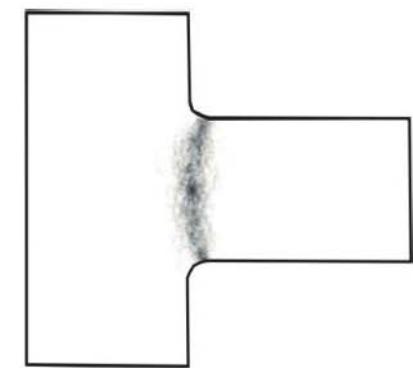
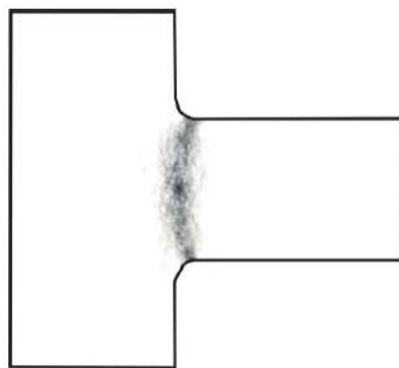


bending-dominated
loading



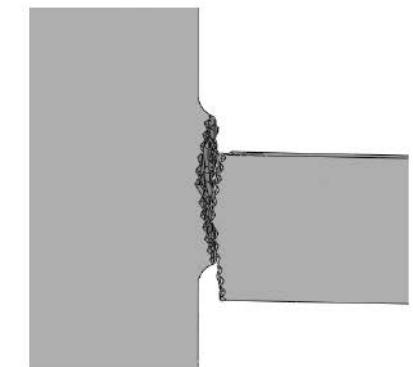
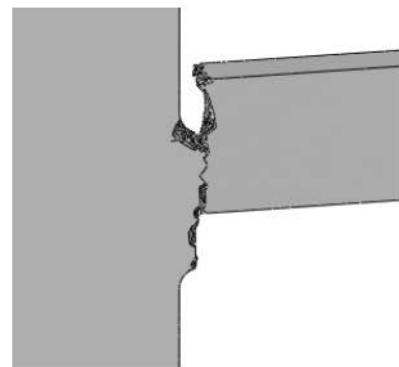
Micro-scale:

loci of max failure probability
due to quasi-brittle cracking



Meso-scale:

failure mode due
to brittle cracking

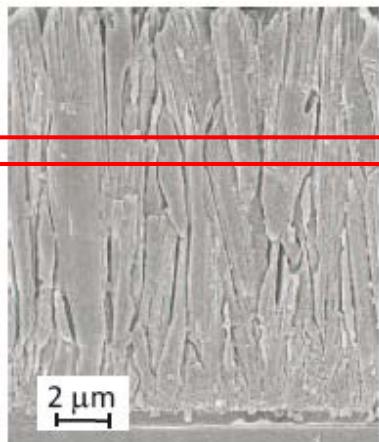


Topics to discuss:

- 1. Meso-scale elastic properties**
- 2. Meso-scale elastic domain (strength)**
- 3. Micro-scale quasi-brittle cracking**

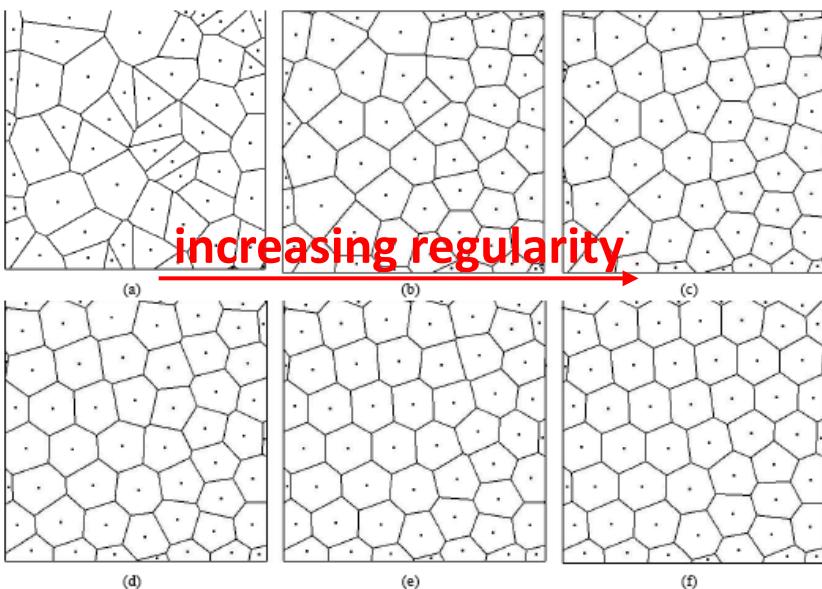
Meso-scale elastic properties

Columnar polysilicon film
(lateral view)



taking a slice of the film
(plane stress cond.)

regularized Voronoi tessellations



Through homogenization: in-plane macro strain and stress vectors

$$\mathbf{E} = \{E_{11} \ E_{22} \ E_{12}\}^T$$

$$\boldsymbol{\Sigma} = \{\Sigma_{11} \ \Sigma_{22} \ \Sigma_{12}\}^T$$

defined as volume averages, according to:

$$\boldsymbol{\Sigma} = \frac{1}{V} \int_V \boldsymbol{\sigma} dV$$

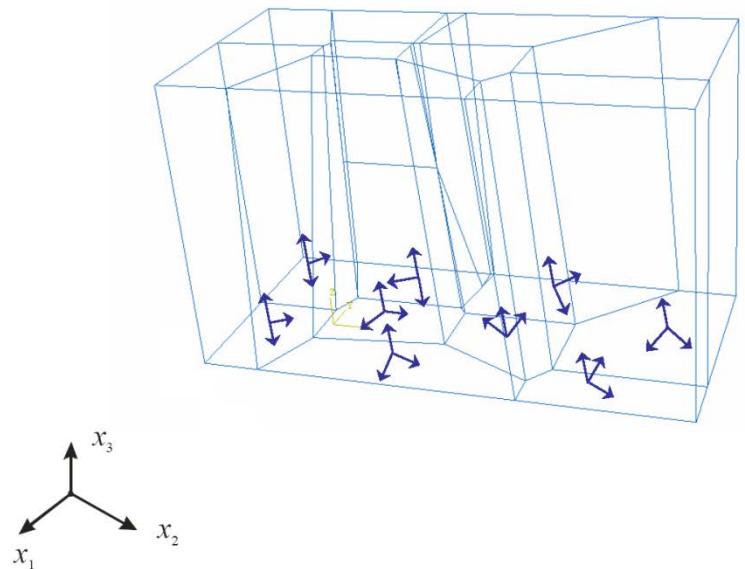
local elastic law

$$\boldsymbol{\sigma} = \mathbf{C} \boldsymbol{\varepsilon}$$

$$\mathbf{E} = \frac{1}{V} \int_V \boldsymbol{\varepsilon} dV$$

Polysilicon assumed to feature:

- one axis of elastic symmetry aligned with epitaxial growth direction x_3
- random orientation of other two elastic symmetry directions in the x_1 - x_2 plane



Matrix of elastic moduli for single-crystal Si
(FCC symmetry)

$$\mathbf{c} = \begin{bmatrix} 165.7 & 63.9 & 63.9 & 0 & 0 & 0 \\ 63.9 & 165.7 & 63.9 & 0 & 0 & 0 \\ 63.9 & 63.9 & 165.7 & 0 & 0 & 0 \\ 0 & 0 & 0 & 79.6 & 0 & 0 \\ 0 & 0 & 0 & 0 & 79.6 & 0 \\ 0 & 0 & 0 & 0 & 0 & 79.6 \end{bmatrix} GPa$$

Reference value for nominal tensile strength (depending on the local loading mode)

$$\sigma_c = 2 \div 4 \text{ GPa}$$

Elastic moduli in $\Sigma = CE$ are numerically bounded through:

- uniform strain boundary cond.

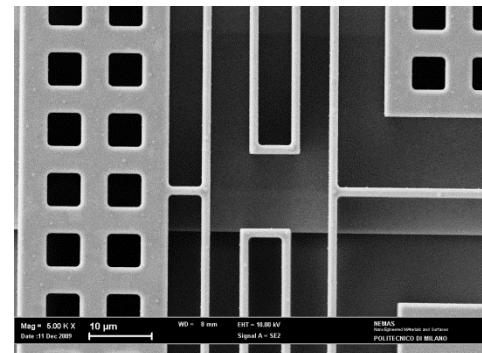
$$\mathbf{u} = \mathbf{X}\mathbf{E} \quad \text{on} \quad \partial V$$

$$\mathbf{X} = \begin{bmatrix} x_1 & 0 & \frac{x_2}{2} \\ 0 & x_2 & \frac{x_1}{2} \end{bmatrix}$$

- uniform stress boundary cond.

$$\mathbf{T} = \mathbf{N}\Sigma \quad \text{on} \quad \partial V$$

$$\mathbf{N} = \begin{bmatrix} n_1 & 0 & n_2 \\ 0 & n_2 & n_1 \end{bmatrix}$$



Voigt and **Reuss** bounds:

from Hill-Mandel macro-homogeneity condition $\Sigma^T E = \frac{1}{V} \int_V \sigma^T \varepsilon dV = \frac{1}{V} \int_V \sigma_l^T \varepsilon_l dV$

Voigt assumption: $\varepsilon = E$ everywhere

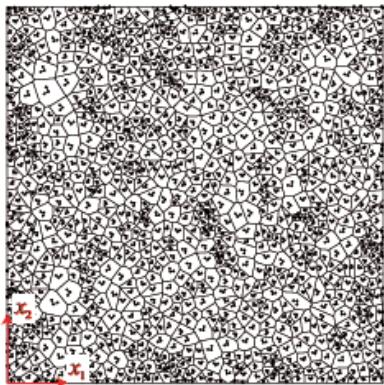
$$E^T C E = \frac{1}{V} \int_V \varepsilon_l^T c_l \varepsilon_l dV = \frac{1}{V} \int_V \varepsilon^T t_\varepsilon^T c_l t_\varepsilon \varepsilon dV = E^T \left[\frac{1}{V} \int_V t_\varepsilon^T c_l t_\varepsilon dV \right] E = E^T \left[\frac{1}{V} \int_V c dV \right] E$$

$$\rightarrow C = \frac{1}{V} \int_V t_\varepsilon^T c_l t_\varepsilon dV$$

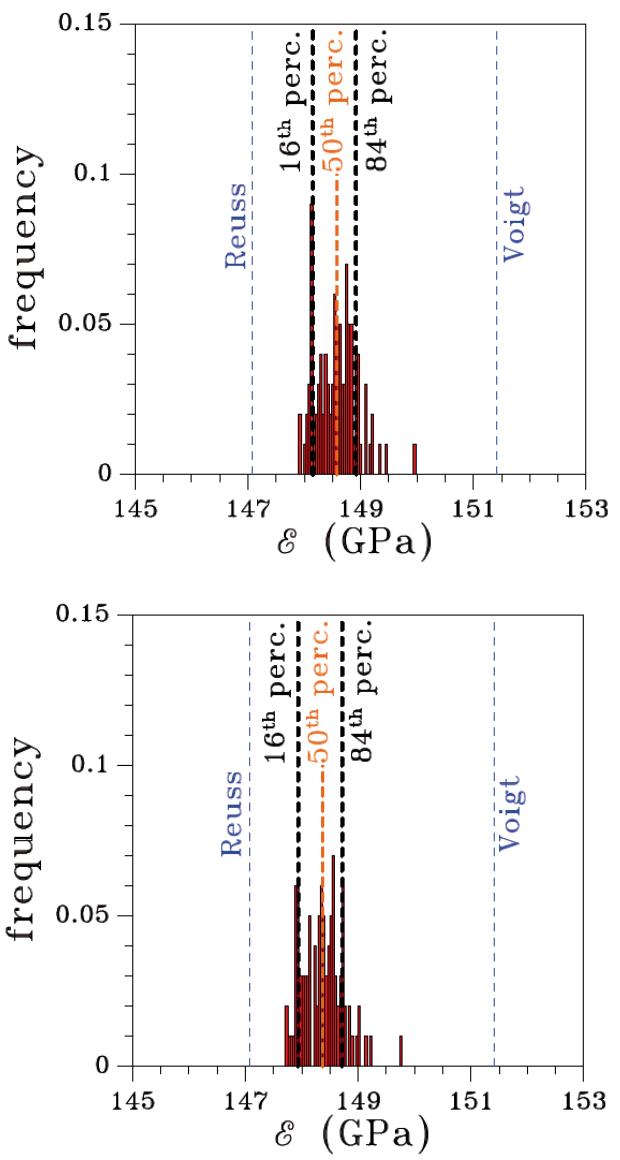
Reuss assumption: $\sigma = \Sigma$ everywhere

$$\rightarrow C^{-1} = \frac{1}{V} \int_V t_\sigma^T c_l^{-1} t_\sigma dV$$

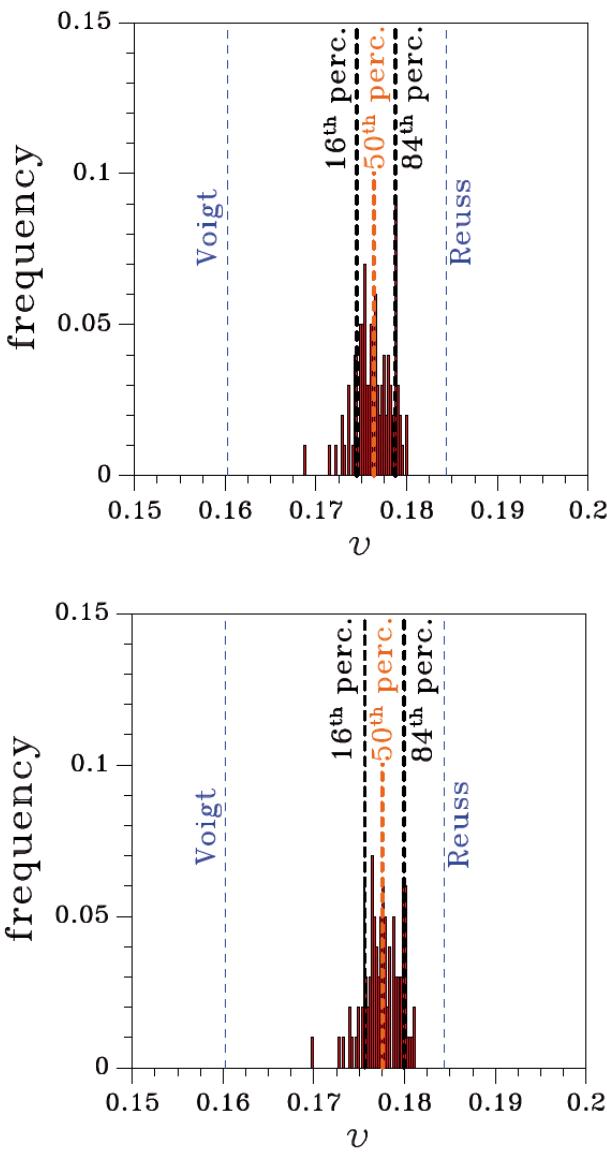
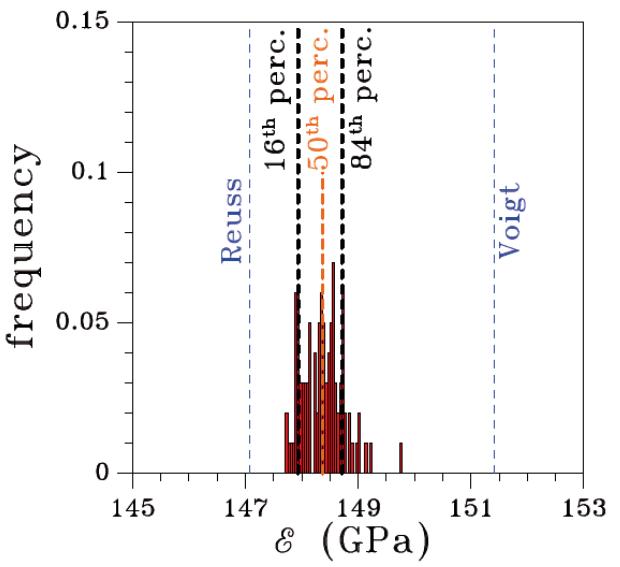
$$L = 12 \text{ } \mu\text{m}, \\ \bar{s}_g = 0.2 \text{ } \mu\text{m}$$



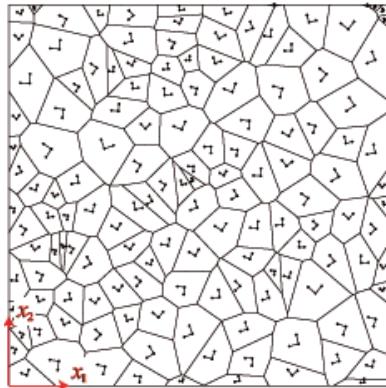
$$u = X E \text{ on } \partial V$$



$$T = N \Sigma \text{ on } \partial V$$

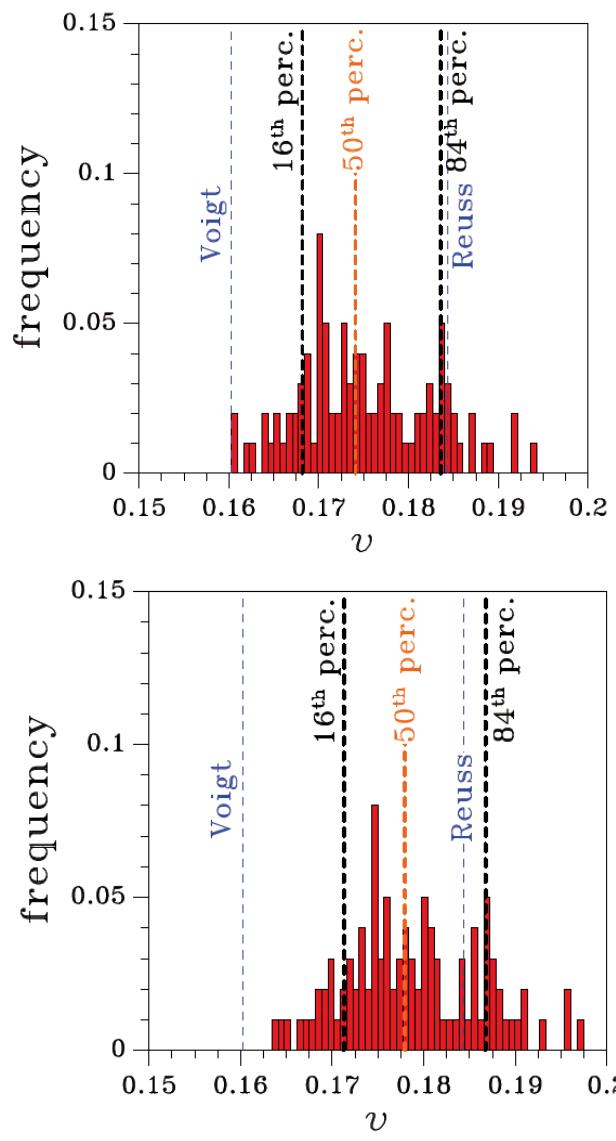
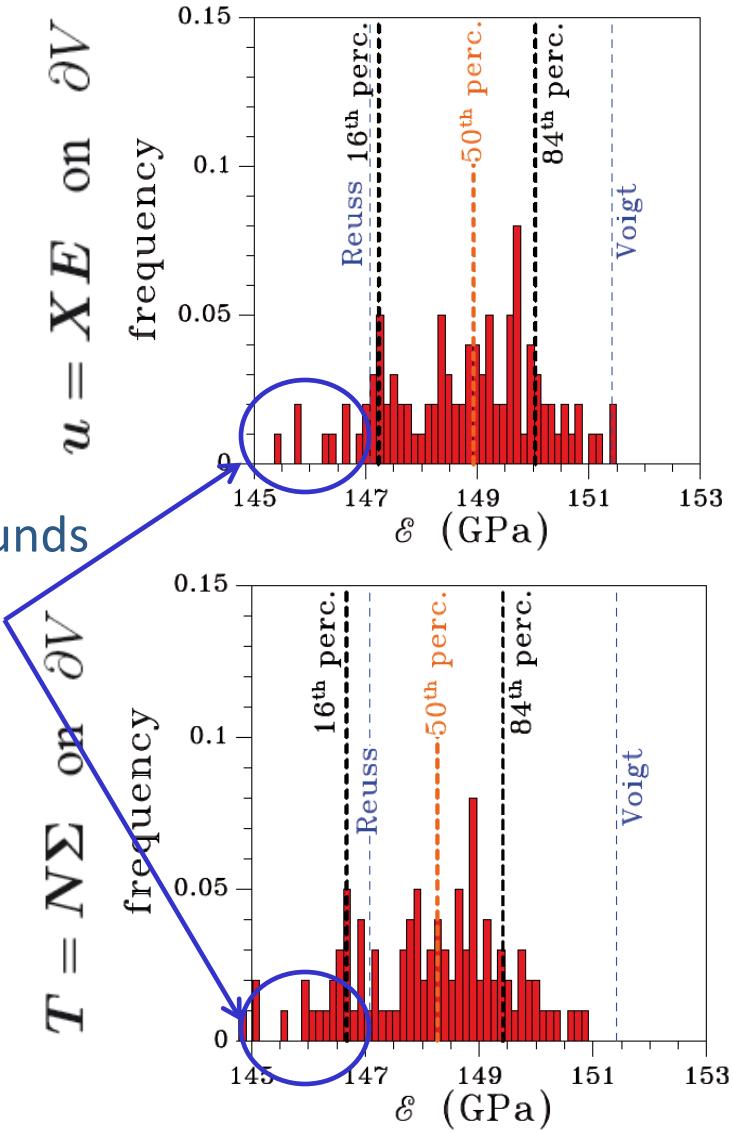


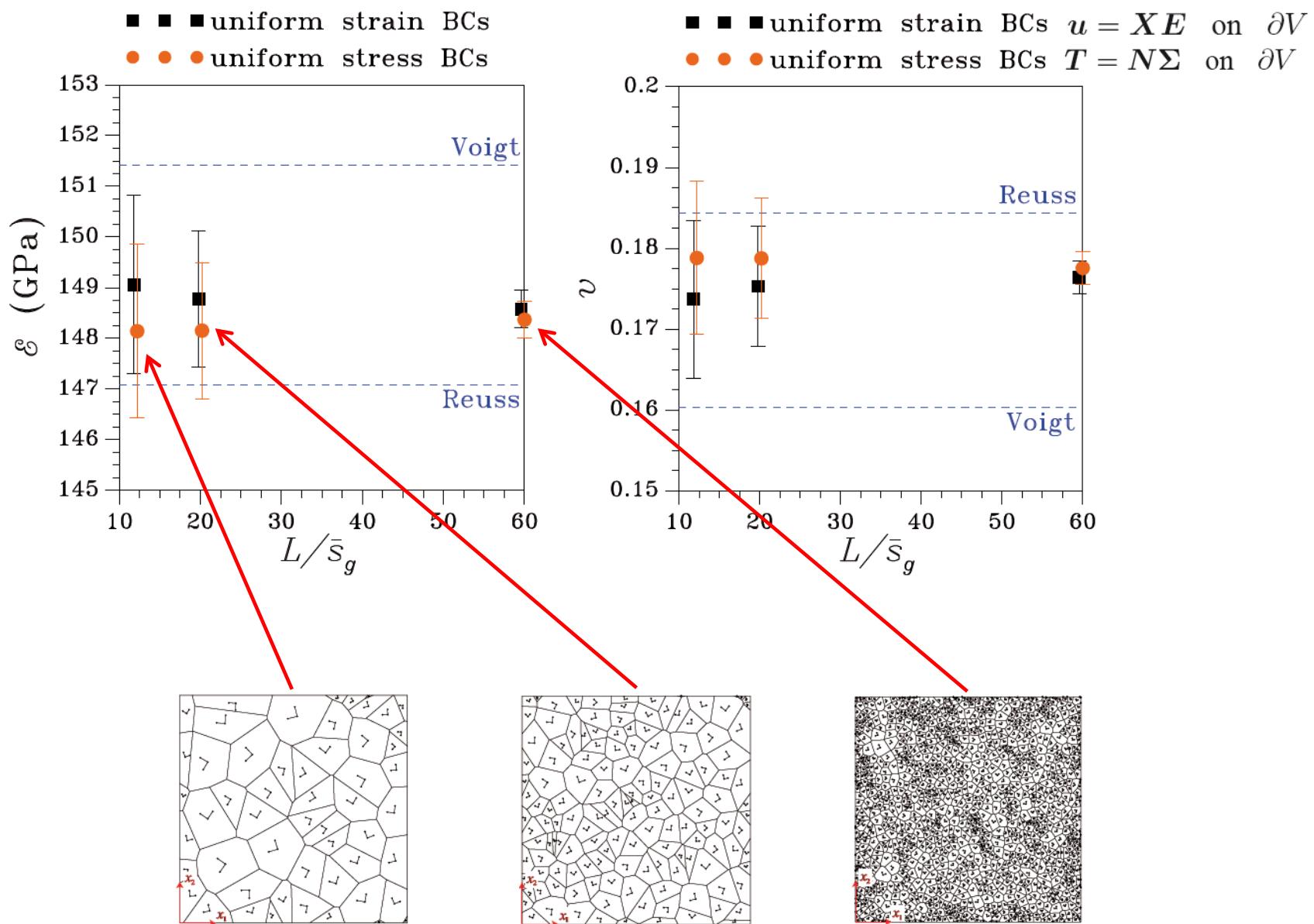
$$L = 12 \text{ } \mu\text{m}, \\ \bar{s}_g = 0.6 \text{ } \mu\text{m}$$



Results exceeding bounds
(why?)

$$C = \frac{1}{V} \int_V t_\varepsilon^T c_l t_\varepsilon dV$$



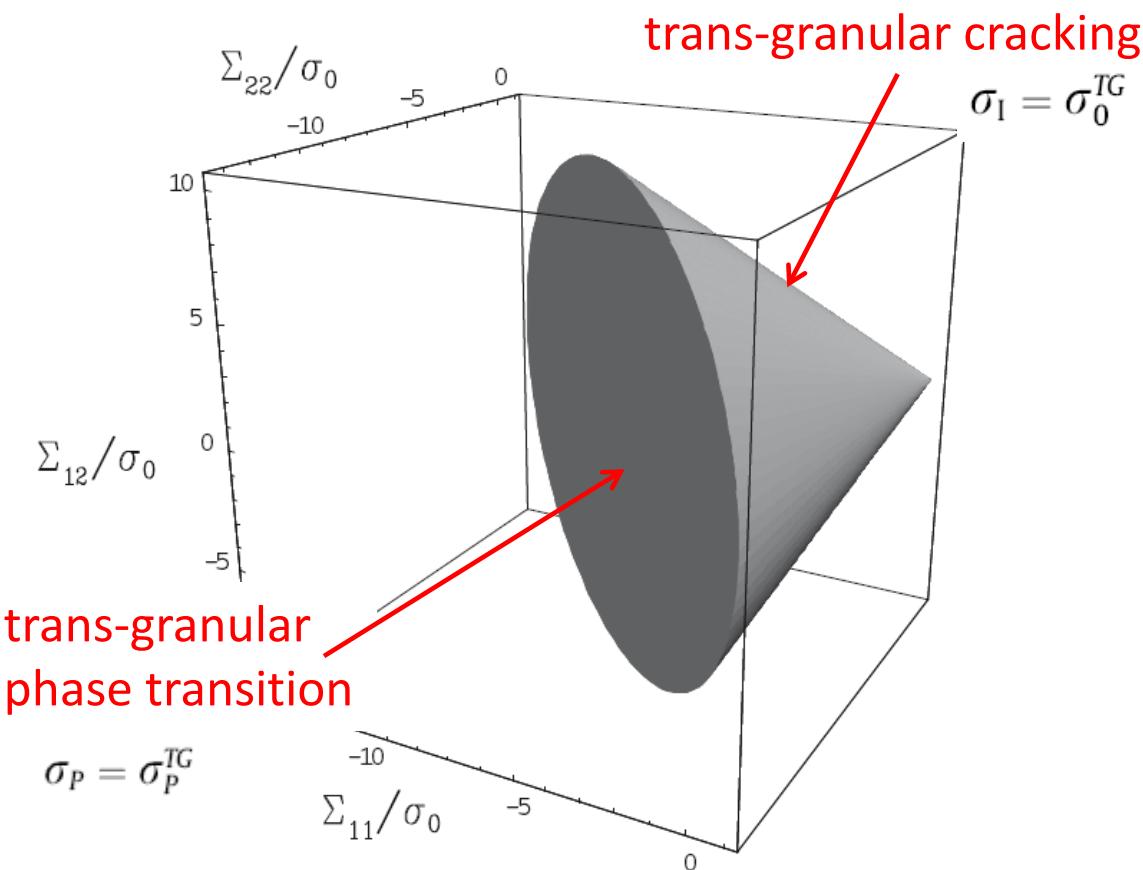


Meso-scale elastic domain (strength)

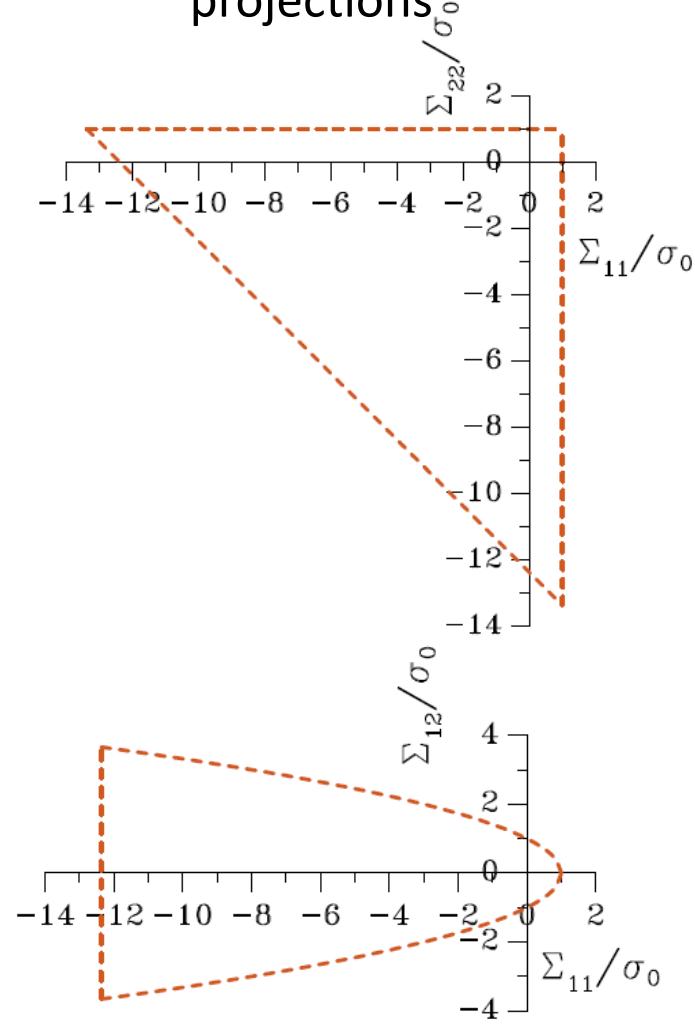
Micro-scale analysis: upscaling of elastic domain (strength)

Elastic domain of single-crystal Si (plane-stress)

3D view

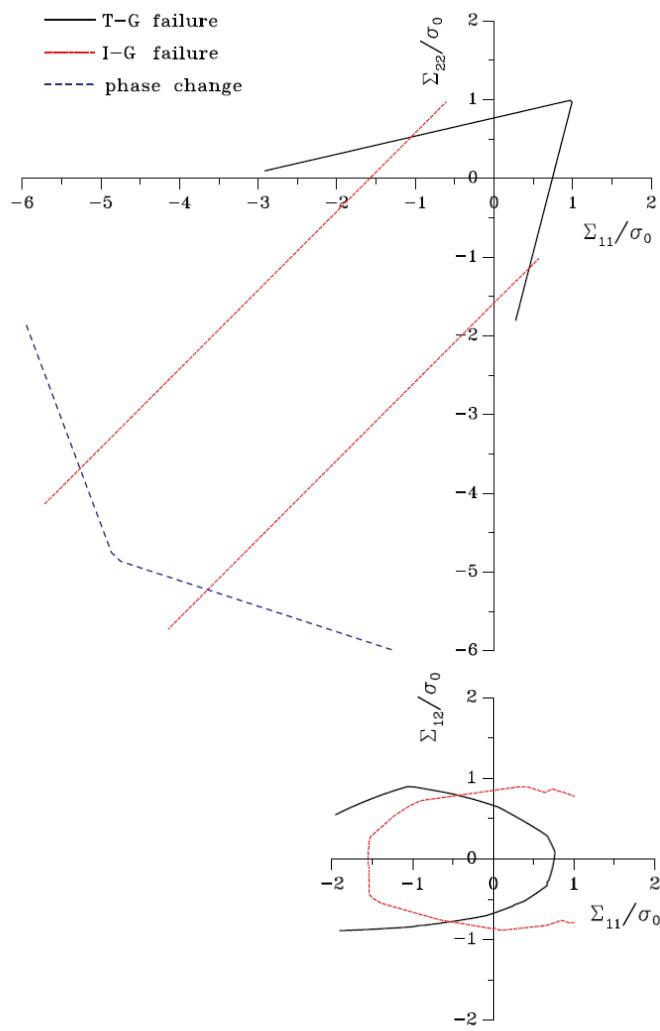


projections

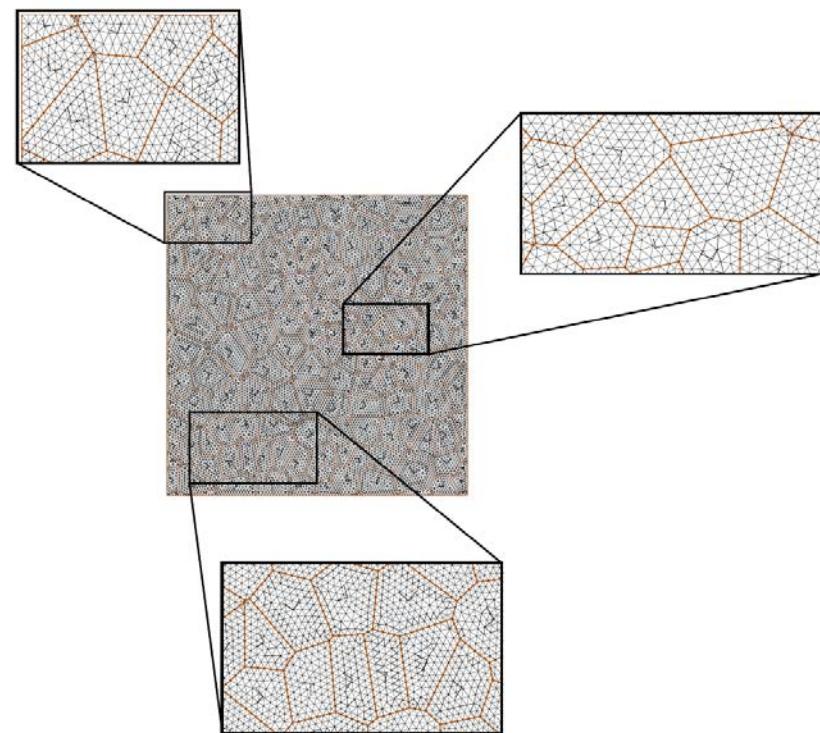


Micro-scale analysis: upscaling of elastic domain (strength)

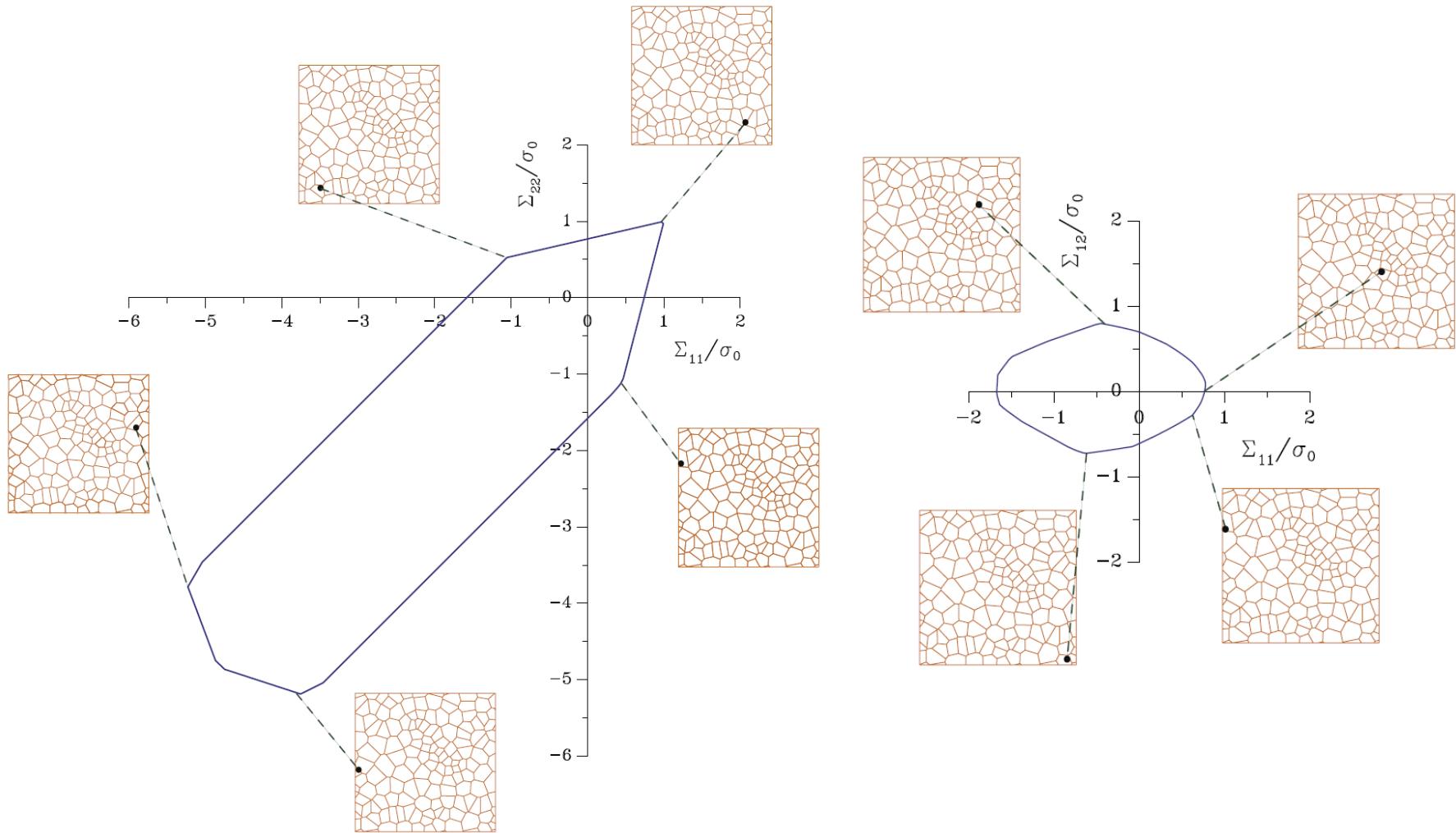
Adding the inter-granular cracking condition $\sigma = \sqrt{\langle \sigma_n \rangle^2 + \frac{1}{\beta^2} \sigma_s^2} = \sigma_0^{IG}$ [Camacho-Ortiz], under uniform strain BCs



adopted space discretization
to resolve stress-state along GBs



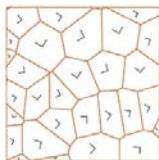
Localization of the failing points for some stress states



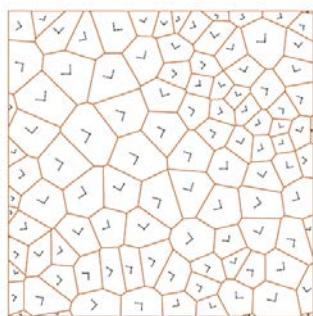
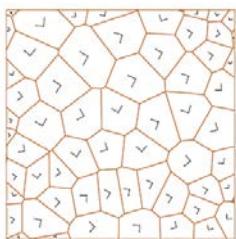
Micro-scale analysis: upscaling of elastic domain (strength)

Effect of RVE size on the shape of elastic domain ($d_e = 0.2 \mu\text{m}$)

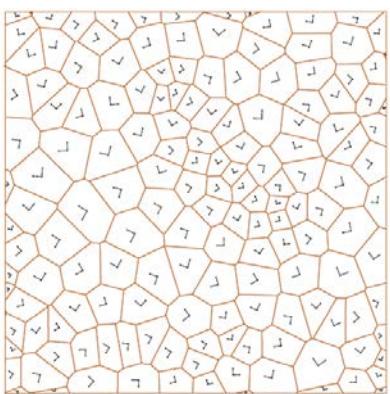
$L=8 \mu\text{m}$



$L=12 \mu\text{m}$

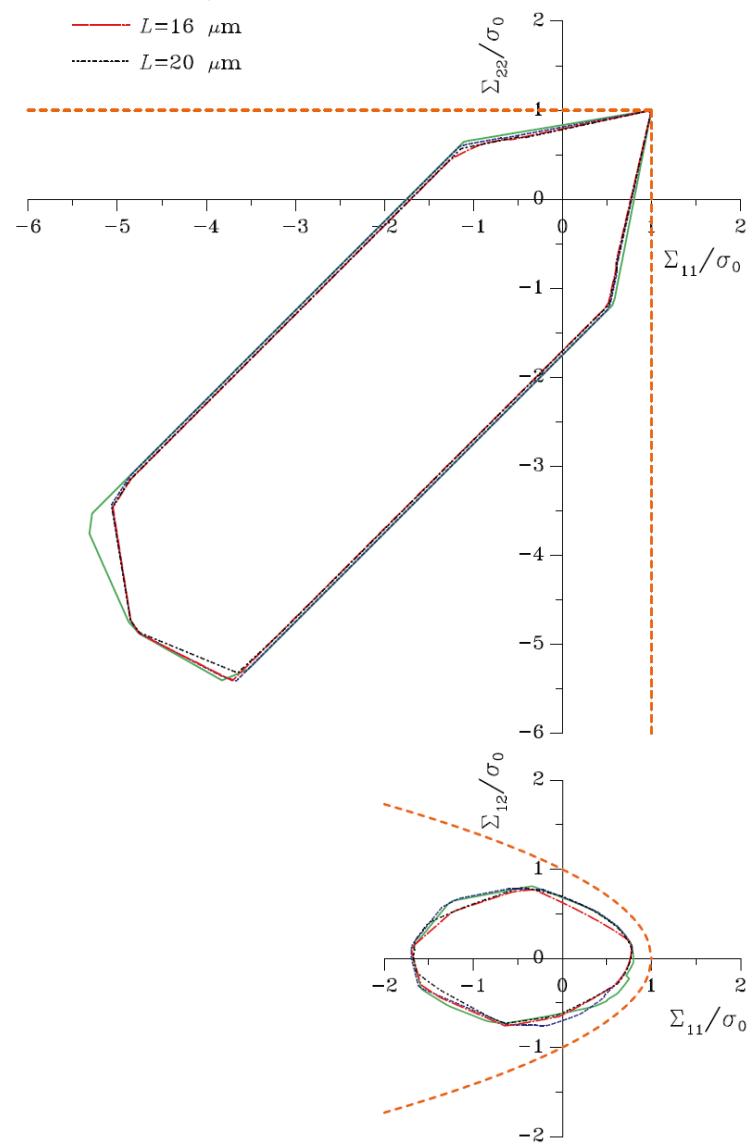


$L=16 \mu\text{m}$



$L=20 \mu\text{m}$

- $L=8 \mu\text{m}$
- - - $L=12 \mu\text{m}$
- $L=16 \mu\text{m}$
- $L=20 \mu\text{m}$



Micro-scale quasi-brittle cracking

Weak form of incremental equilibrium

$$\int_{\Omega \setminus \Gamma_d} \gamma^T \dot{\boldsymbol{\sigma}} d\Omega = \int_{\Omega \setminus \Gamma_d} \mathbf{v}^T \dot{\mathbf{b}} d\Omega + \int_{\Gamma_t} \mathbf{v}^T \dot{\mathbf{t}} d\Gamma_t - \int_{\Gamma_d} [\mathbf{v}]^T \dot{\mathbf{t}} d\Gamma_d \quad \forall \mathbf{v} \in \mathcal{U}_0$$

\mathbf{v} is the test function

$$\gamma = \mathbf{C}\mathbf{v}$$

\mathcal{U} is the trial solution space

(\mathbf{u} continuous in $\Omega \setminus \Gamma_d$, possibly discontinuous along Γ_d)

\mathcal{U}_0 is the variation space

(\mathbf{v} continuous in $\Omega \setminus \Gamma_d$, possibly discontinuous along Γ_d , $\mathbf{v} = \mathbf{0}$ on Γ_u)

Allowing for bulk and interface constitutive models

$$\begin{aligned} \text{find } \mathbf{u} \in \mathcal{U} : \int_{\Omega \setminus \Gamma_d} \gamma^T \mathbf{E}_\Omega(\mathbf{x}) \boldsymbol{\varepsilon} d\Omega + \int_{\Gamma_d} [\mathbf{v}]^T \mathbf{E}_\Gamma(\mathbf{x}) [\dot{\mathbf{u}}] d\Gamma_d \\ = \int_{\Omega \setminus \Gamma_d} \mathbf{v}^T \dot{\mathbf{b}} d\Omega + \int_{\Gamma_t} \mathbf{v}^T \dot{\mathbf{t}} d\Gamma_t \quad \forall \mathbf{v} \in \mathcal{U}_0 \end{aligned}$$

Effective displacement discontinuity [Camacho&Ortiz]:

$$[u] = \sqrt{[u]_n^2 + \beta^2 [u]_s^2}$$

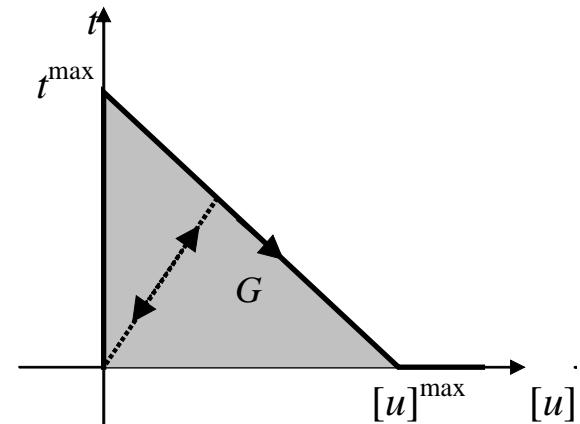
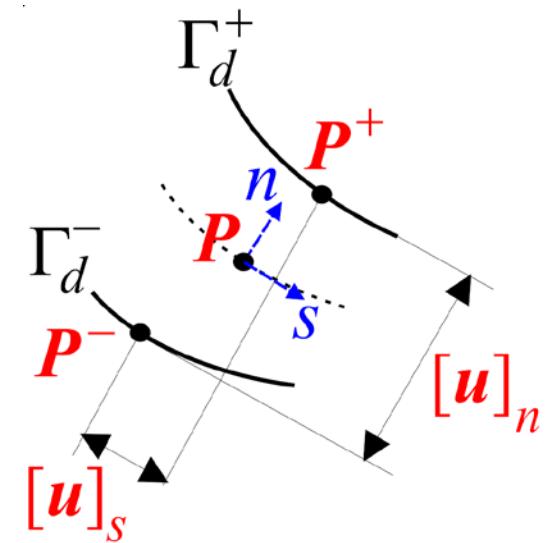
opening (mode I) component
 sliding (mode II) component

work conjugate effective traction:

$$t = \sqrt{t_n^2 + \frac{1}{\beta^2} t_s^2}$$

Irreversible effective cohesive law

- linear envelope: $t = t^{\max} \left(1 - \frac{[u]}{[u]^{\max}} \right)$
- unloading to the origin of the t - $[u]$ plane;
- fracture energy: $G = t^{\max} [u]^{\max} / 2$



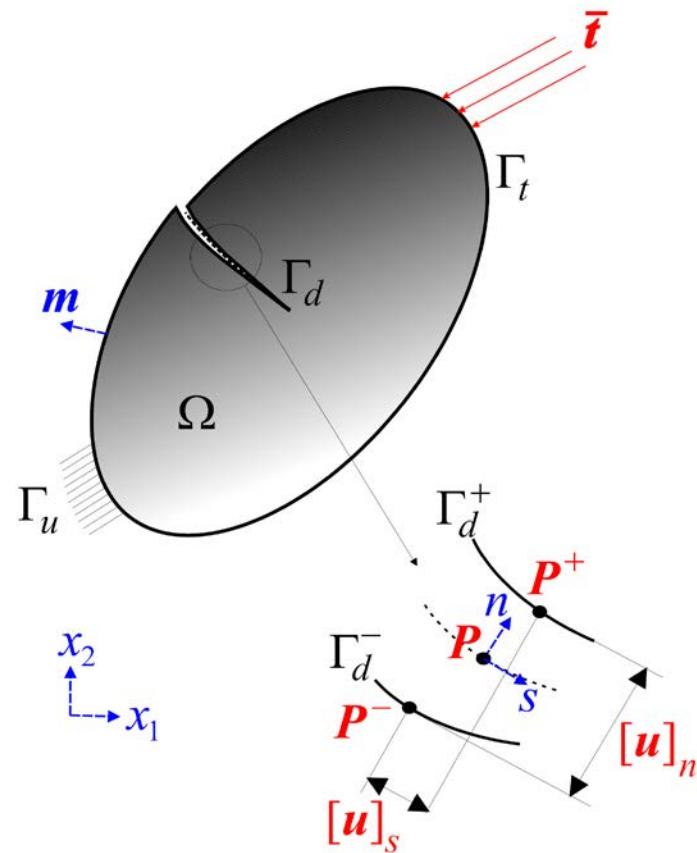
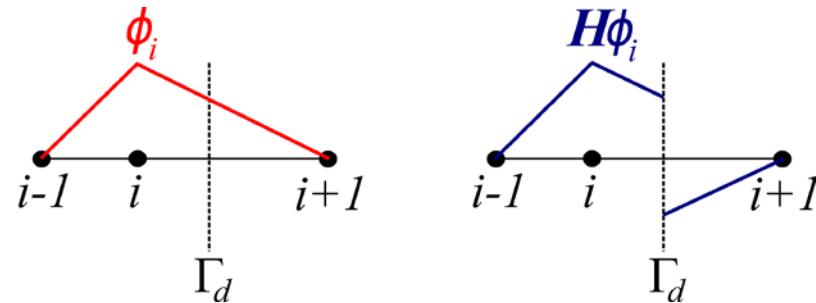
Enhanced FE discretized model, discontinuous along Γ_d :

nodal shape functions

$$\mathbf{u}^h(\mathbf{x}) = \sum_{i \in I} \phi_i(\mathbf{x}) \mathbf{u}_i^0 + \sum_{j \in J} H(\mathbf{x}) \phi_j(\mathbf{x}) \mathbf{u}_j^E$$

generalized Heaviside step-function

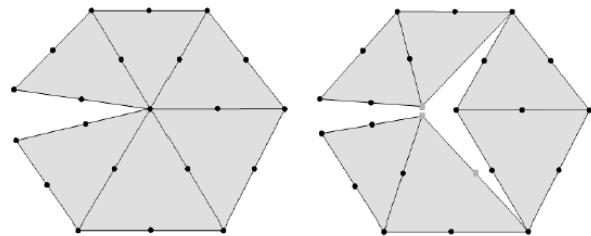
$$\mathcal{H}(\mathbf{x}) = \begin{cases} +1 & \text{if } (\mathbf{x} - \mathbf{x}^*)^\top \mathbf{n} > 0 \\ -1 & \text{if } (\mathbf{x} - \mathbf{x}^*)^\top \mathbf{n} < 0 \end{cases}$$



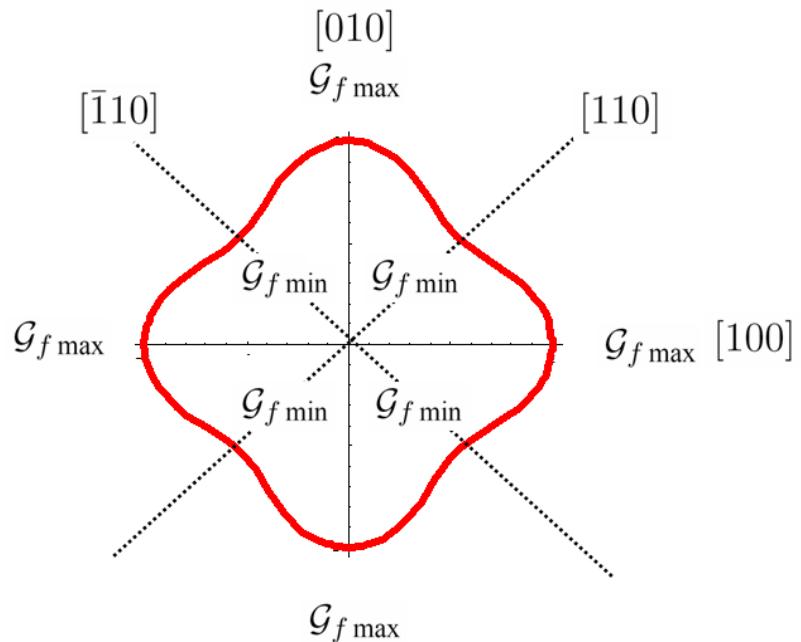
- enhancement restricted to the j nodes whose supports are crossed by the crack
- local refinement with limited increase of DOFs

[Tanaka et alii, IJF]

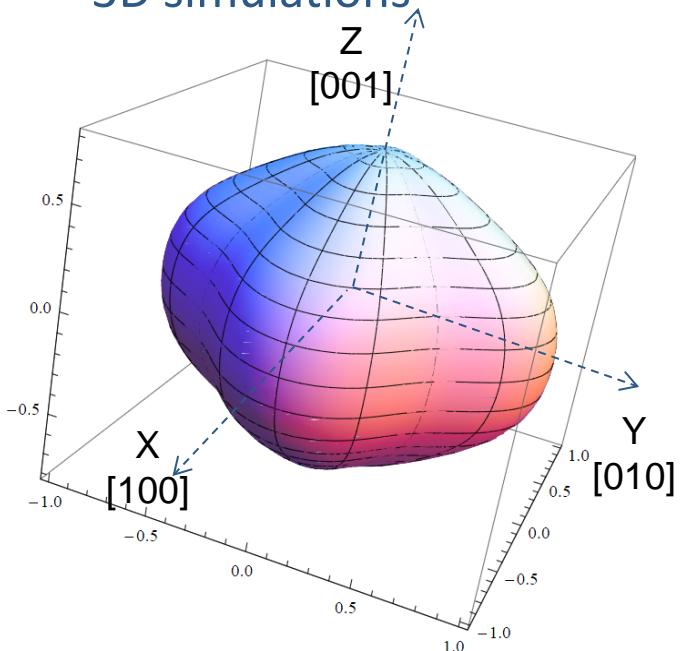
- Transgranular fracture energy assumed to smoothly vary, depending on the relative orientation of crack plane and grain crystal lattice
- Transgranular strength independent of the orientation



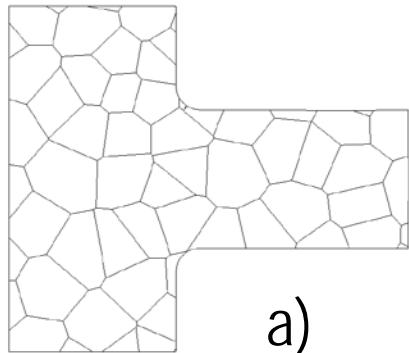
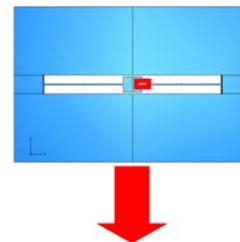
2D simulations



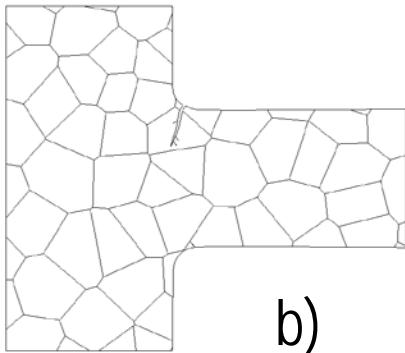
3D simulations



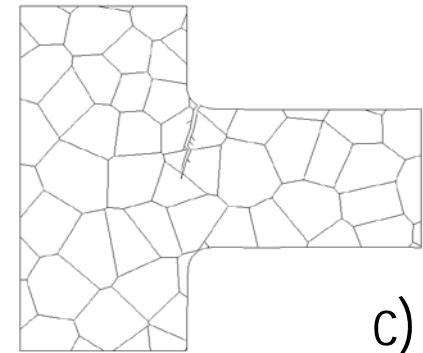
Depending on the falling orientation,
crack may start from one of the two reentrant corners
at the end of each suspension spring



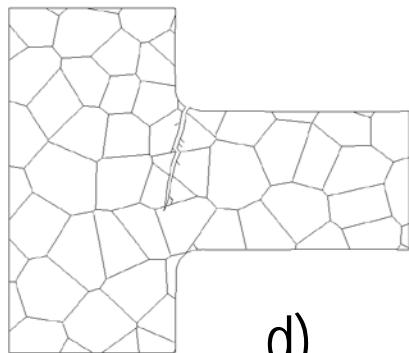
a)



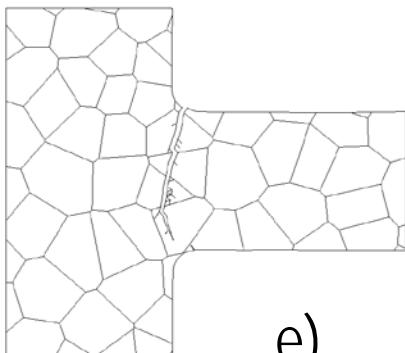
b)



c)



d)

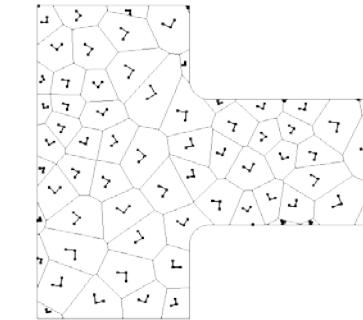
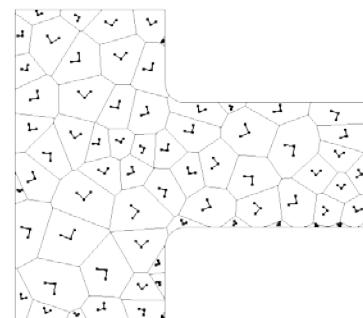
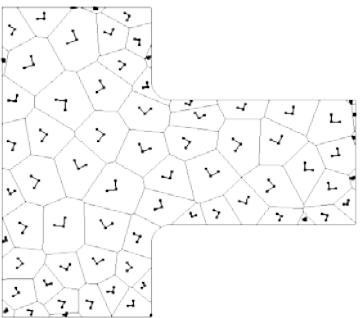
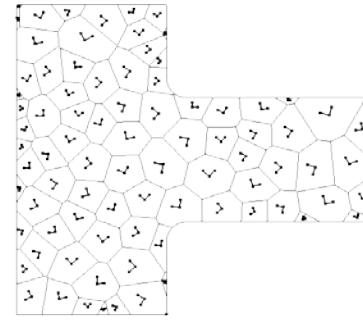
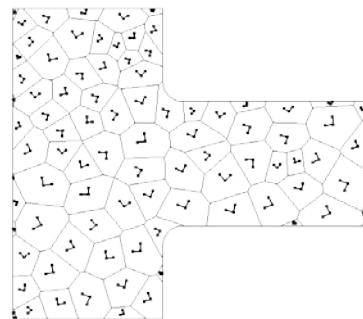
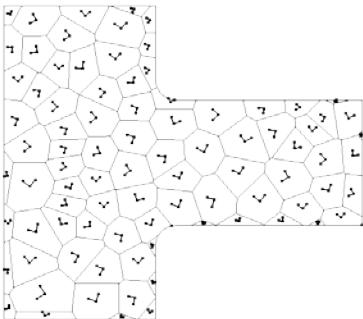


e)

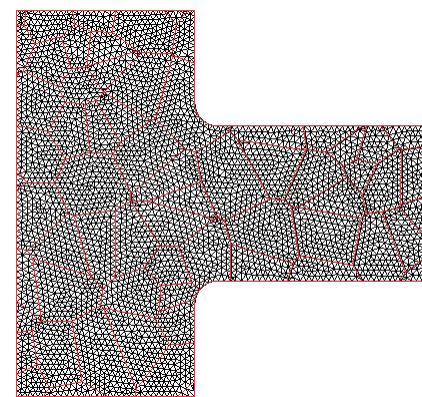
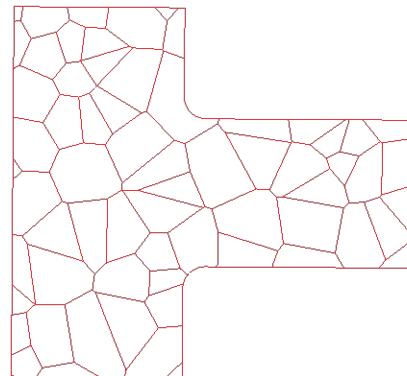


f)

Monte Carlo simulations are carried out with different grain morphologies and crystal orientations



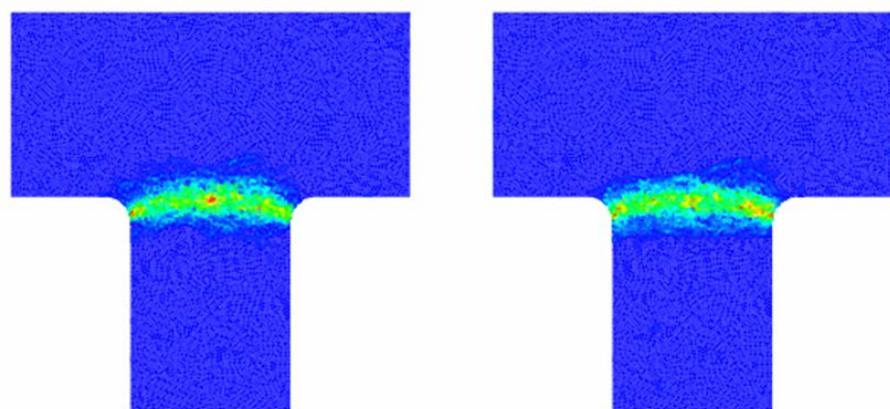
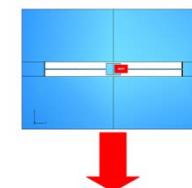
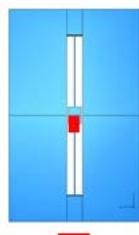
tessellation



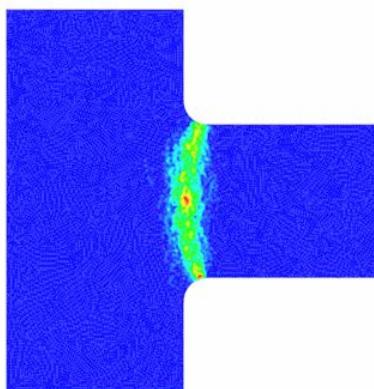
FE mesh

Failure probability map:

at convergence of the statistics of the Monte Carlo simulation, map of probability for a crack to pass by that point



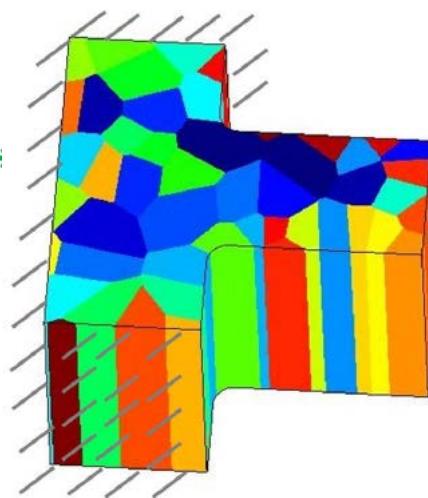
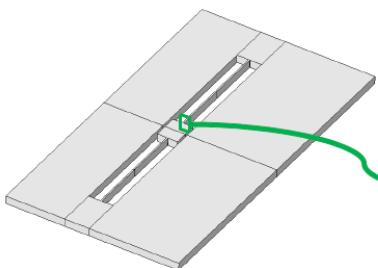
Reduced (-20%) tensile strength
at grain boundaries



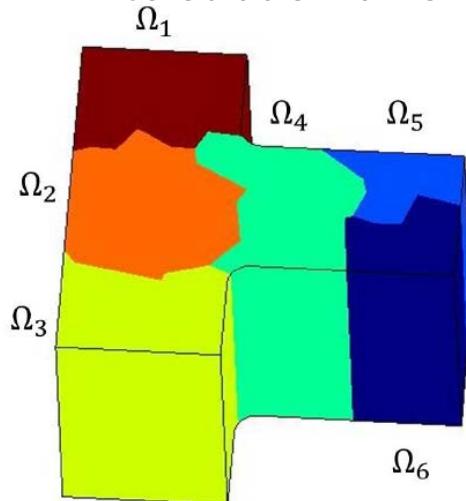
Reduced (-20%) tensile strength
at grain boundaries

Micro-scale analysis:

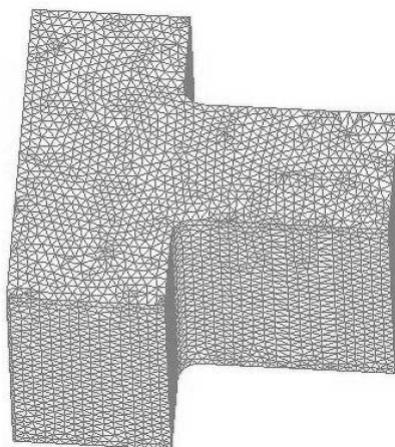
3D forecast of crack pattern at failure



Mesh partition
into subdomains

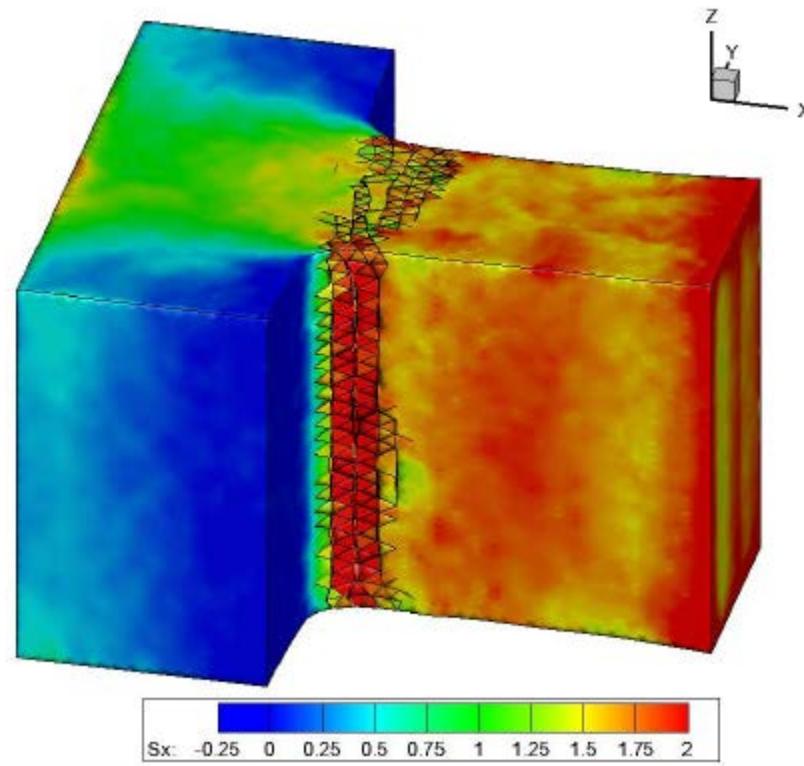


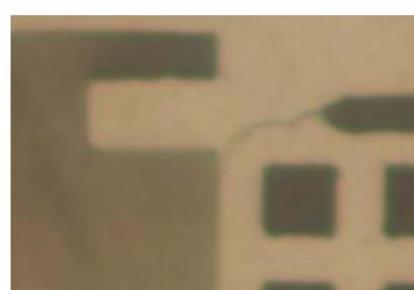
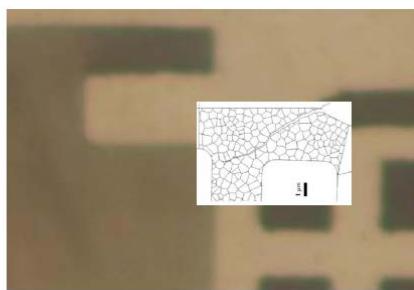
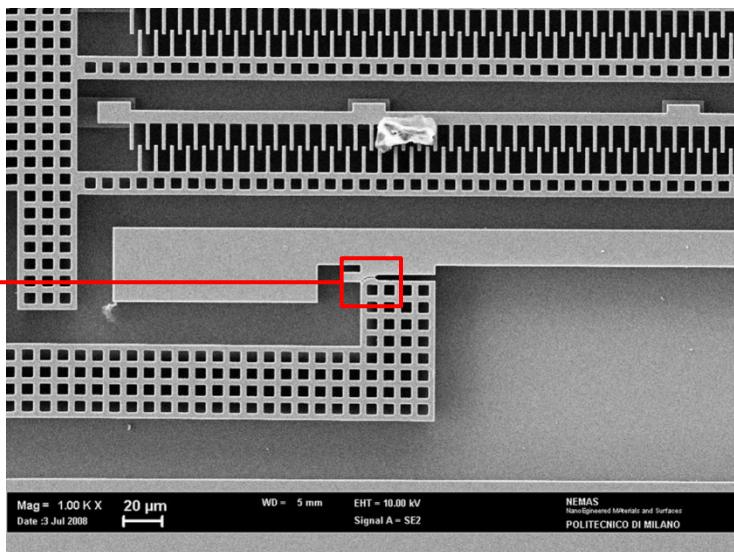
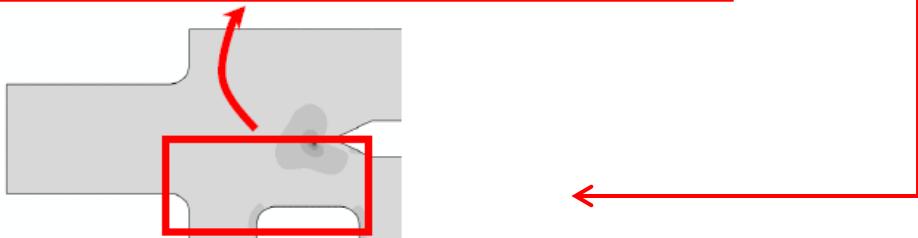
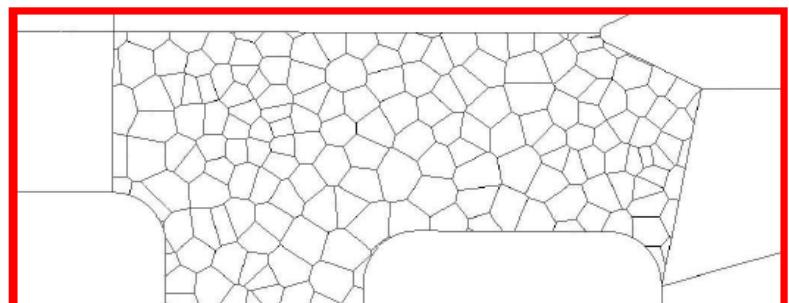
FE mesh



FE mesh	
Number of elements	142,648 quad tetra
Number of nodes	202,286
DOFs	606,858

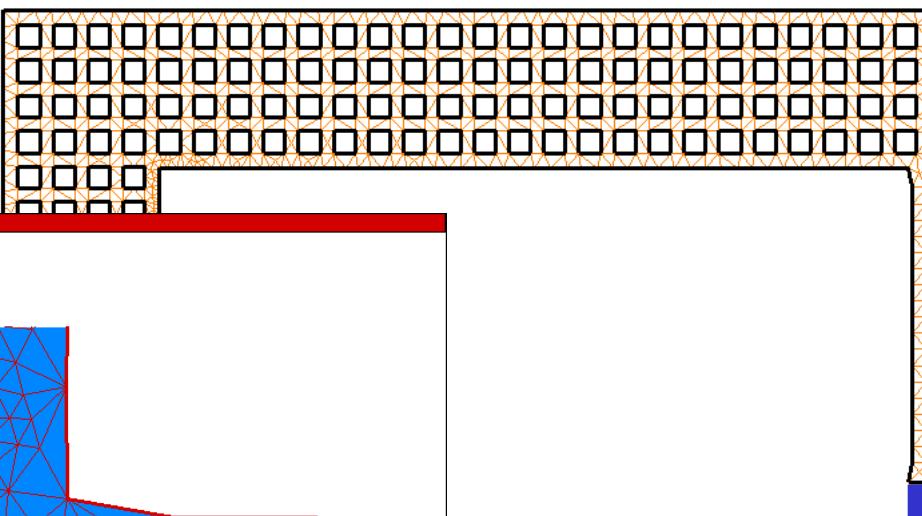
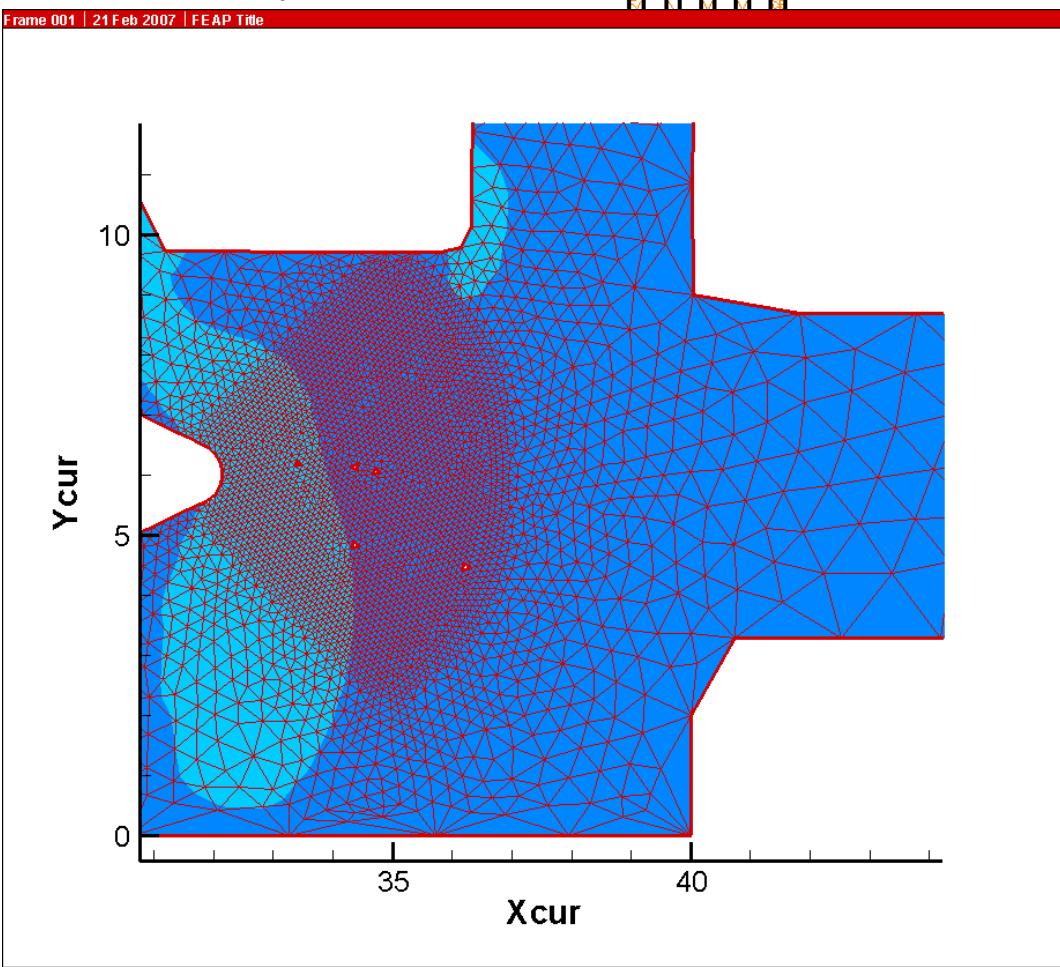
crack pattern at failure





Full coupling of meso- and micro-scale analyses: a proposal based on Partition of Unity (X-FEM)

Proposal of a test-structure
to measure polysilicon
toughness (on-chip test)



Mesh layout does not
depend on crystal topology



Monte-Carlo simulations
by changing the crystal
morphology without
modifying FE mesh

3D modeling of crack initiation and propagation:

- choice of the optimal partitioning approach (regular, automatic decomposer, grain-based, element size-based) for domain decomposition, and adaptive partitioning during crack growth
- simultaneous handling of implicit/explicit time integration techniques
- parallel implementation in an MPI environment

Multi-physics (thermo-electro-magneto-mechanical) simulations

- reduced order modeling through POD (proper orthogonal decomposition)

Acknowledgments

- Italian MIUR-PRIN projects “*Mechanics of microstructured materials: multi-scale identification, optimization and active control*” and “*Multi-scale, multi-physics and domain decomposition methods in the mechanics of microsystems and nano and micro-structured materials*”
- Regione Lombardia and CILEA-CINECA Consortium, grants: *M²-MEMS, POLYFRAC*

Thank you for your attention!